United States Patent [19]

Mick

[11] **Patent Number:** **5,828,606**

[45] **Date of Patent:** **Oct. 27, 1998**

[54] **FULLY SYNCHRONOUS PIPELINED RAM**

[75] Inventor: **John R. Mick**, San Jose, Calif.

[73] Assignee: **Integrated Device Technology, Inc.,** Santa Clara, Calif.

[21] Appl. No.: **864,289**

[22] Filed: **May 28, 1997**

Related U.S. Application Data

[62] Division of Ser. No. 635,128, Apr. 19, 1996.

[51] **Int. Cl.**^{6} **G11C 13/00**
[52] **U.S. Cl.** **365/189.05**; 365/189.01; 365/193; 365/191
[58] **Field of Search** 365/189.01, 189.05, 365/193, 191

[56] **References Cited**

U.S. PATENT DOCUMENTS

4,882,709	11/1989	Wyland	365/189.02
5,515,325	5/1996	Wada	365/189.01
5,526,320	6/1996	Zagar et al.	3645/233.5
5,546,344	8/1996	Fawcett	365/189.05
5,568,430	10/1996	Ting	365/189.05
5,577,236	11/1996	Johnson et al.	395/551
5,617,362	4/1997	Mori et al.	365/189.05
5,644,729	7/1997	Amini et al.	395/250
5,652,724	7/1997	Manning	365/189.05
5,659,696	8/1997	Amini et al.	395/412
5,663,901	9/1997	Wallace et al.	365/52
5,675,549	10/1997	Ong et al.	365/233.5
5,699,317	12/1997	Sartore et al.	365/230.06

OTHER PUBLICATIONS

Prince, *Semiconductor Memories: A Handbook of Design, Manufacture and Application*, 2d ed., 1991, pp. 467–472.

Primary Examiner—Viet Q. Nguyen
Attorney, Agent, or Firm—Skjerven, Morrill, MacPherson, Franklin & Friel

[57] **ABSTRACT**

A memory system includes a memory, an input circuit and a logic circuit. The input circuit is coupled to receive a memory address and, during a write operation, the corresponding write data to be written into the SRAM. The logic circuit causes the write data to be stored in the input circuit for the duration of any sequential read operations immediately following the write operation and then to be read into the memory during subsequent write operation. During the read operation, data which is stored in the write data storage registers prior to being read into the memory can be read out from the memory system should the address of one or more read operations equal the address of the data to be written into the memory while temporarily stored in the write data storage registers. Thus, no "bus turnaround" down time is experienced by the system thereby increasing the bandwidth of the system. The system can operate in a single pipeline mode or a dual pipeline mode.

3 Claims, 21 Drawing Sheets
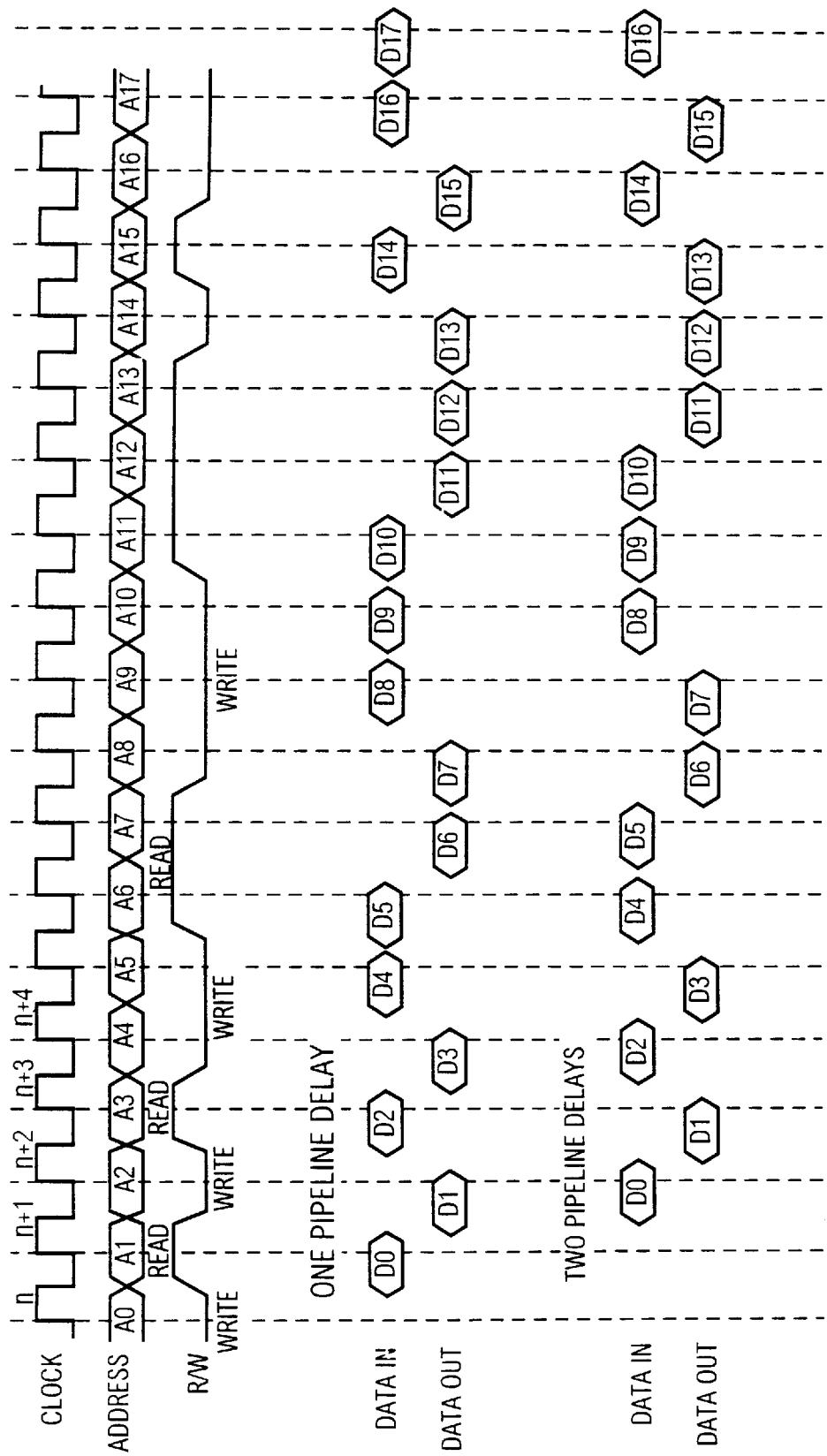
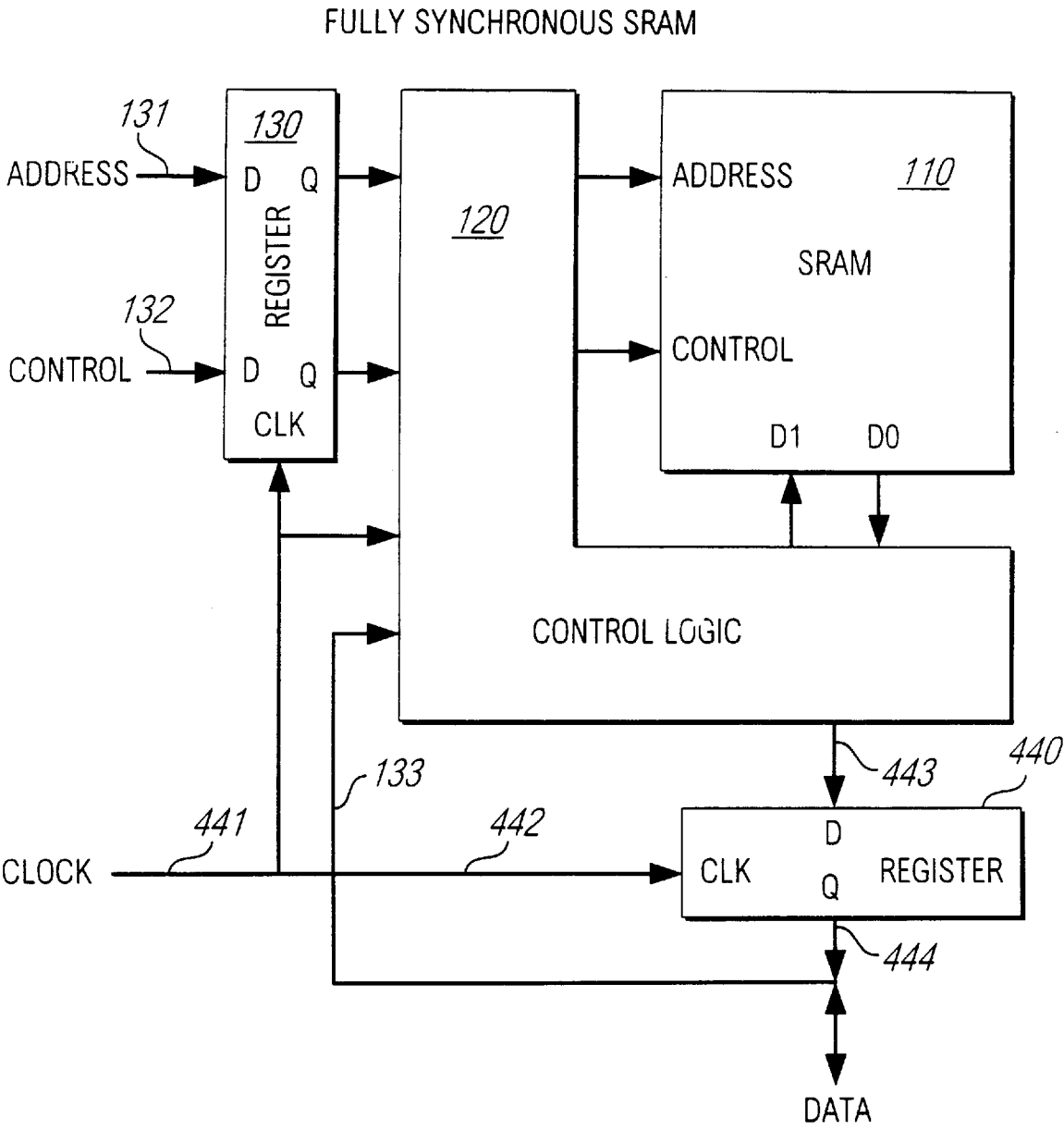FULLY SYNCHRONOUS SRAM

FIG. 1

FIG. 2

SYNCHRONOUS SRAM TIMING DIAGRAM

FIG. 3

FULLY SYNCHRONOUS SRAM

FIG. 4

CLOCK CYCLE	0	1	2	3	4	5	6	7	8
ADDRESS	A0	A1	A2	A3	A4	A5	A6	A7	A8
	R	R	W	R	W	W	R		
		READ	READ	WRITE	READ	WRITE	WRITE	READ	
		A0	A1	A2	A3	A4	A5		
DATA OUT			D0	D1		D3			
DATA IN					D2		D4	D5	

DOUBLE PIPE READ

FIG. 5C

ADDRESS WRITE DATA IN X

DOUBLE PIPE WRITE

FIG. 5B

ADDRESS SRAM READ DATA OUT

DOUBLE PIPE READ

FIG. 5A

FULLY SYNCHRONOUS, DOUBLE PIPELINED SRAM

FIG. 6A-1

FIG. 6A

| FIG. 6A-1 |
| FIG. 6A-2 |

FIG. 6A-2

FULLY SYNCHRONOUS, DOUBLE PIPELINED SRAM

FIG. 6B-1

FIG. 6B

FIG. 6B-1
FIG. 6B-2

FIG. 6B-2

FIG. 7-1

FIG. 7-2

FIG. 7

FIG. 7-1	FIG. 7-2

FIG. 7A

CLOCK ⟶ CK

Eq2 *701-1*   Eq3 *701-2*   Eq4 *701-3*

EQUAL   EQUAL   EQUAL

702

+1

703-1 *704-1*   *704-2*

H

ADDRESS ⟶ MUX

L

CnT/LOAD* ⟶

D Q
E
REG   A1

CpEn*

D Q
E
REG   A2

CpEn* *705-1*

D

704-3

D Q
E
REG   A3

704-4

D Q
E
REG

706-1 *707-1*

R/W* ⟶ OR

D Q
E
REG   R1

CpEn*

INVERT — W1

D Q
E
REG   R2

705-2

INVERT — W2

CK — DELAY

706-2

CpEn*

708-1   *708-2*

CS* ⟶

D Q
E
REG   CS1*

CpEn* ⟶

D Q
E
REG — CS2*

R2 —

706-5

CpEn* —

OR

CS2* —

CpEn*

D Q
REG

INVERT — HOLD

705-3

706-7

W1 —

R2 —

AND — FLIP

710-1

FIG. 7B-1

FIG. 7B-2

FIG. 7B

FIG.7B-1
FIG. 7B-2

FIG. 8A

DOUBLE PIPELINE
FLIP=HIGH OR LOW

ADDRESS REGISTERS	CK	n t_0	$n+1$ t_1	$n+2$ t_2	$n+3$ t_3	$n+4$ t_4	$n+5$ t_5	$n+6$ t_6	$n+7$ t_7	$n+8$ t_8
704-1	I	a_0	a_1	a_2	a_3	a_4	a_5	a_6	a_7	a_8
	O	a_{-1}	a_0	a_1	a_2	a_3	a_4	a_5	a_6	a_7
704-2	I	a_{-1}	a_0	a_1	a_2	a_3	a_4	a_5	a_6	a_7
	O		a_{-1}	a_0	a_1	a_2	a_3	a_4	a_5	a_6
704-3	I		a_{-1}	a_0	a_1	a_2	a_3	a_4	a_5	a_6
	O			a_{-1}	a_{-1}	a_{-1}	a_2	a_3	a_3	a_3
704-4	I			a_{-1}	a_{-1}	a_{-1}	a_2	a_3	a_3	a_3
	O						a_{-1}	a_2	a_2	a_2
707-1	I	r_0	r_1	w_2	w_3	r_4	r_5	w_6	w_7	w_8
(R1)	O	w_{-1}	r_0	r_1	w_2	w_3	r_4	r_5	w_6	w_7
707-2	I	w_{-1}	r_0	r_1	w_2	w_3	r_4	r_5	w_6	w_7
(R2)	O		w_{-1}	r_0	r_1	w_2	w_3	r_4	r_5	w_6
709-1	I		$d_{-1}(IN)$	$d_0(OUT)$	$d_1(OUT)$	$d_2(IN)$	$d_3(IN)$	$d_4(OUT)$	$d_5(OUT)$	$d_6(IN)$
	O			$d_{-1}(IN)$	$d_{-1}(IN)$	$d_{-1}(IN)$	$d_2(IN)$	$d_3(IN)$	$d_3(IN)$	$d_3(IN)$
709-2	I			$d_{-1}(IN)$	$d_{-1}(IN)$	$d_{-1}(IN)$	$d_2(IN)$	$d_3(IN)$	$d_3(IN)$	$d_3(IN)$
	O						$d_{-1}(IN)$	$d_2(IN)$	$d_2(IN)$	$d_2(IN)$
W_1	H	L	L	H	H	L	L	H	H
W_2		H	L	L	H	H	L	L	H
R_1	L	H	H	L	L	H	H	L	L
R_2		L	H	H	L	L	H	H	L
710-2	I									
	O									
DATA	I/O		$d_{-1}(IN)$	$d_0(OUT)$	$d_1(OUT)$	$d_2(IN)$	$d_3(IN)$	$d_4(OUT)$	$d_5(OUT)$	$d_6(IN)$

FIG. 8B

FIG. 9A

FIG. 9B

PIPELINE RRWWRRWWRR TIMING

FIG. 10A

PIPELINE R RWRWR.'/RW TIMING

FIG. 10B

SINGLE PIPELINE DELAY

FIG. 10C

FULLY SYNCHRONOUS PIPELINED RAM

This application is a division of application Ser. No. 08/635,128, filed Apr. 19, 1996.

FIELD OF THE INVENTION

This invention relates to memory circuits and, more particularly, to fully synchronous pipelined random access memory circuits.

BACKGROUND

Many high performance systems require a memory that operates with a fast system clock. Some designers use synchronous random access memories ("RAMs") to meet this system requirement. For example, some synchronous static RAMs (SRAMs) are available which use registers or latches to temporarily store the address and control. These SRAM's use a "pipeline" scheme whereby the address to be accessed is provided during one cycle and, during the next sequential cycle, the data is provided on the data bus. For example, during a read operation, the address from which data is to be read is provided on the nth cycle and the data read from the SRAM is provided on the data bus on the (n+1)th cycle. For write operations, there are SRAMs that provide the address, control and data during the same cycle and there are designs where address and control are provided on the nth cycle and data is provided on the (n+1)th cycle.

The speed of the SRAM is increased because the set-up and hold time for a register or latch is typically much shorter than the time to access the main array of the SRAM (the difference typically being several nanoseconds). The result is to break the operations into shorter cycles. On the (n+1)th cycle, the register or latch provides the stored address to the SRAM's main array along with the data to be written to the stored address, meeting the set-up and hold times for writing to the SRAM's main array. Because of the reduced set-up and hold time for the address and data on the (n+1)th cycle, the SRAM's cycle time, as viewed at the pins of the device, can be significantly reduced. As a result, the frequency of the system clock can be increased.

One problem with conventional SRAM's is that, typically, trying to intermix reads and writes in a high speed system causes a cycle to be "lost" when a memory write is immediately followed by a memory read (i.e., bus turnaround). Generally, a cycle is lost on turnaround because the structure of these RAMs requires an extra cycle to make sure that all of the data is written into the memory before a read operation can be performed. For example, if a write operation is followed by a read operation from the same address, a lost cycle is needed so that the "new" data will be written to the specified address before the read operation is performed on the data stored at th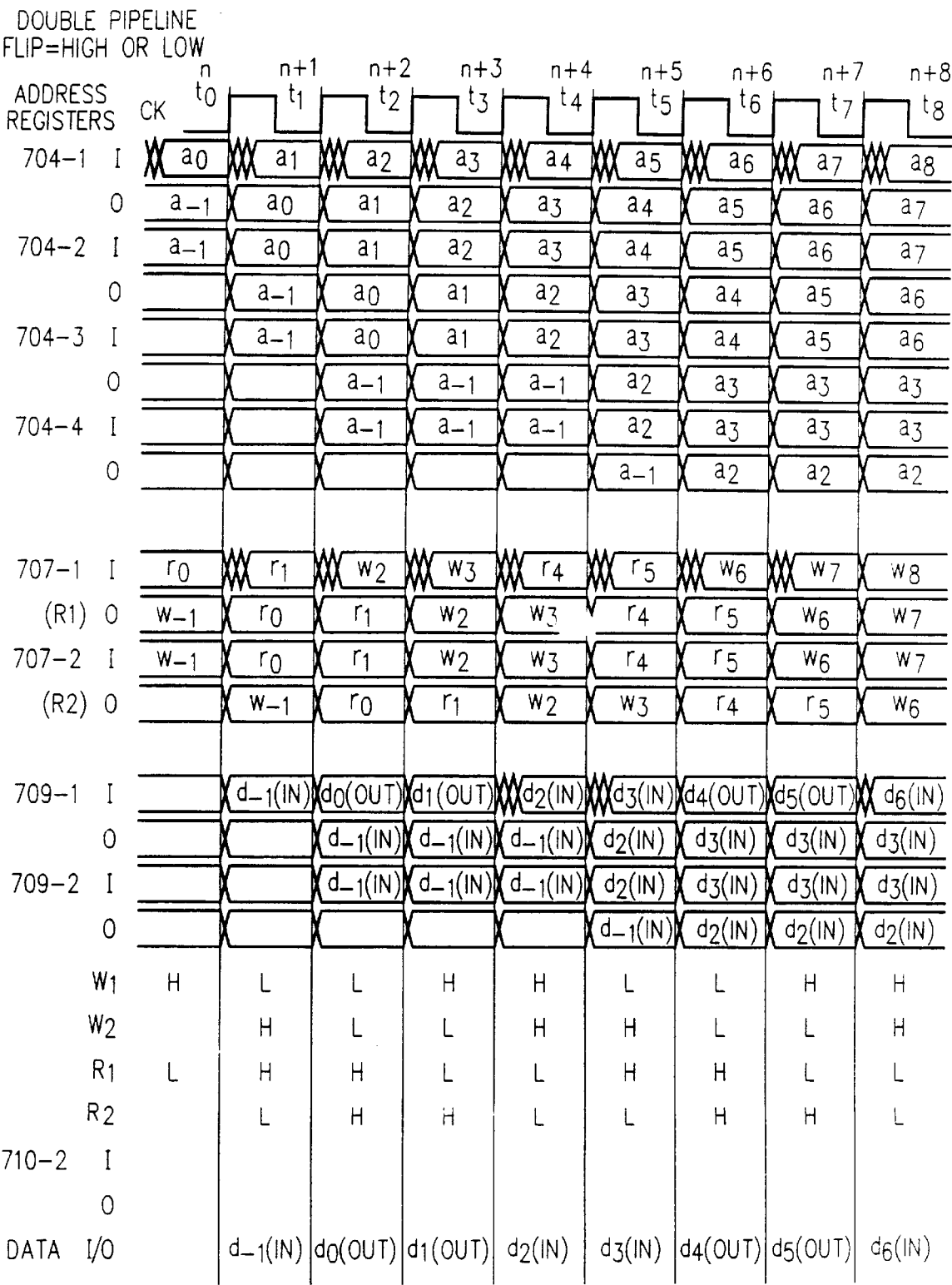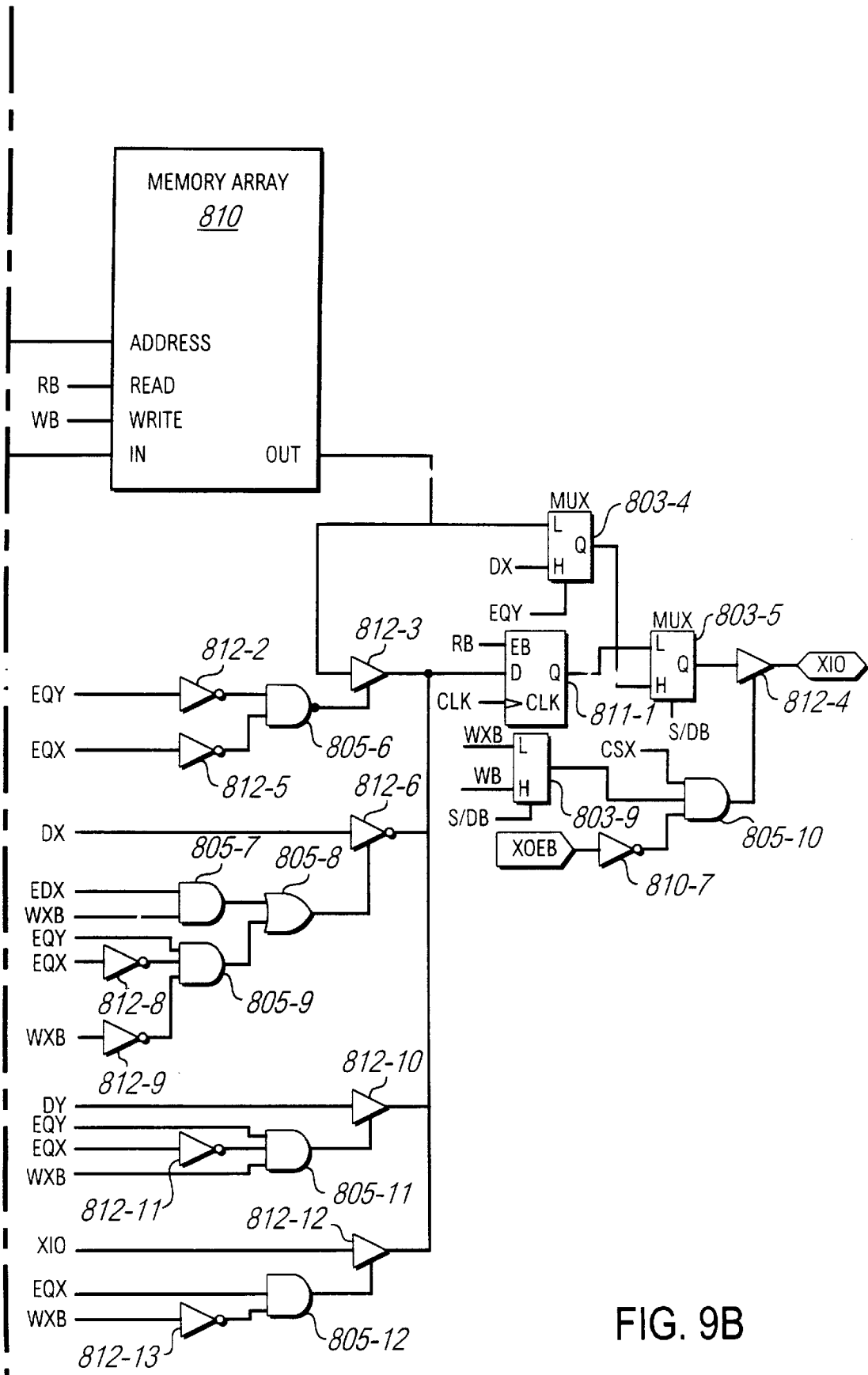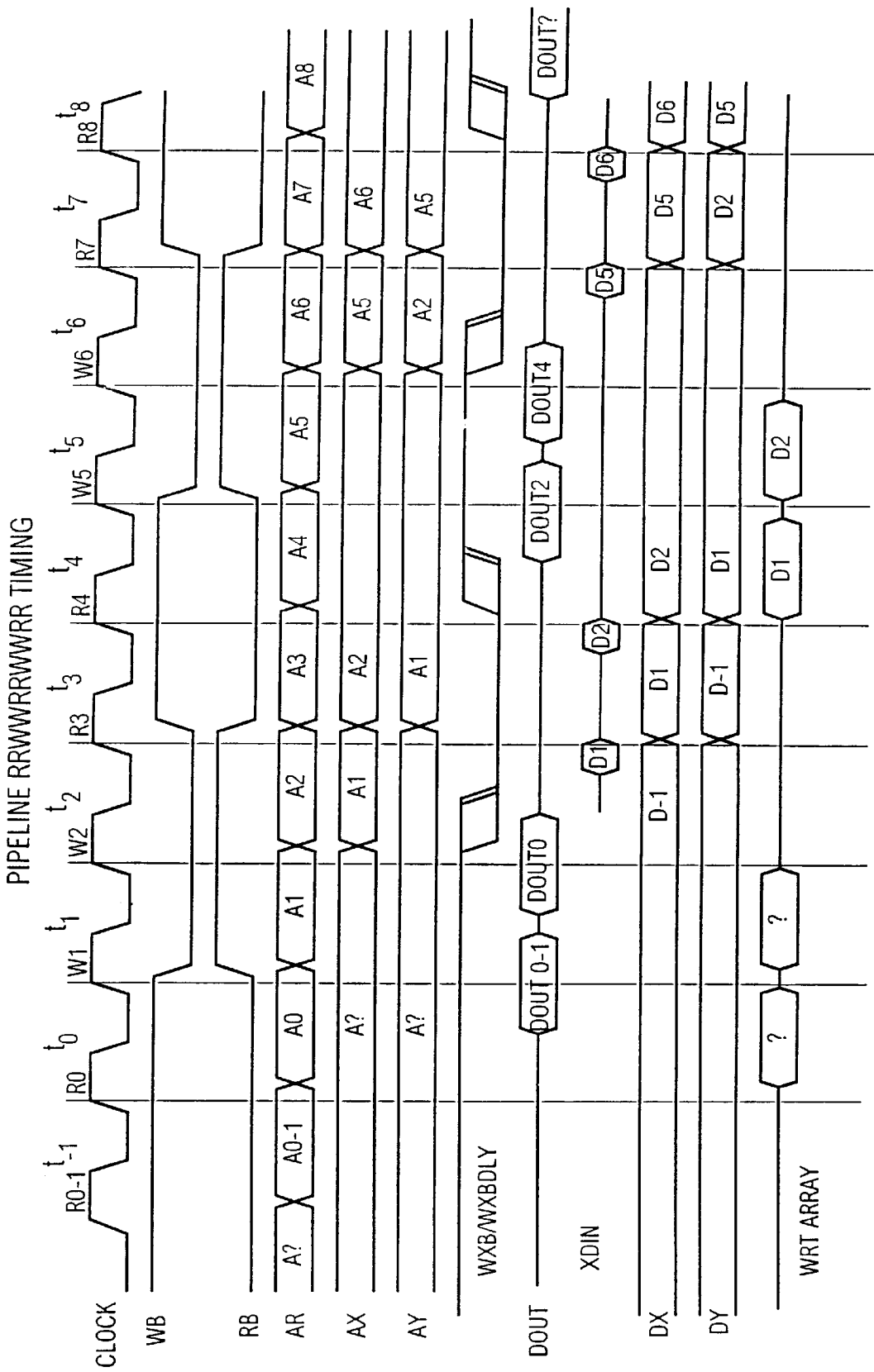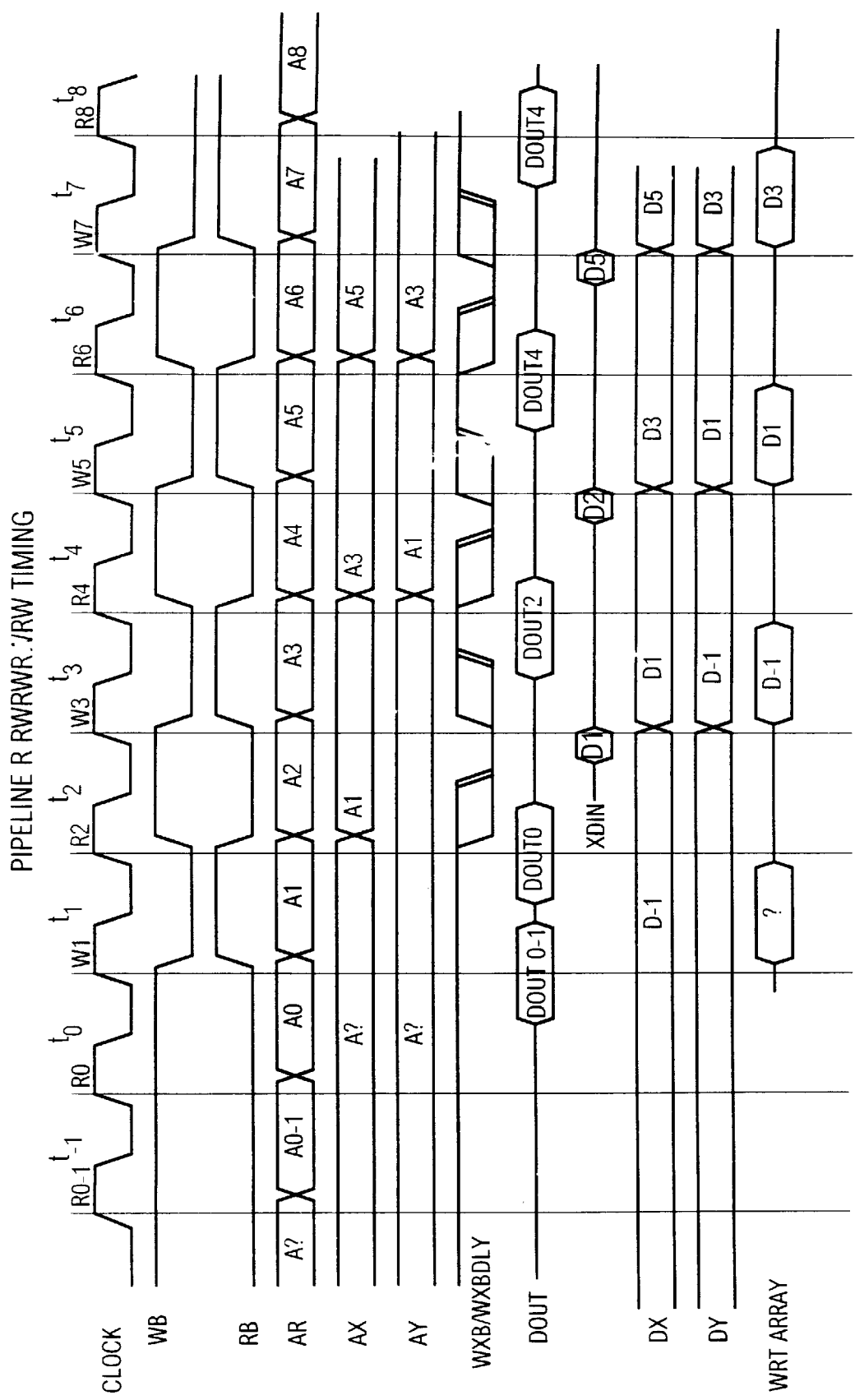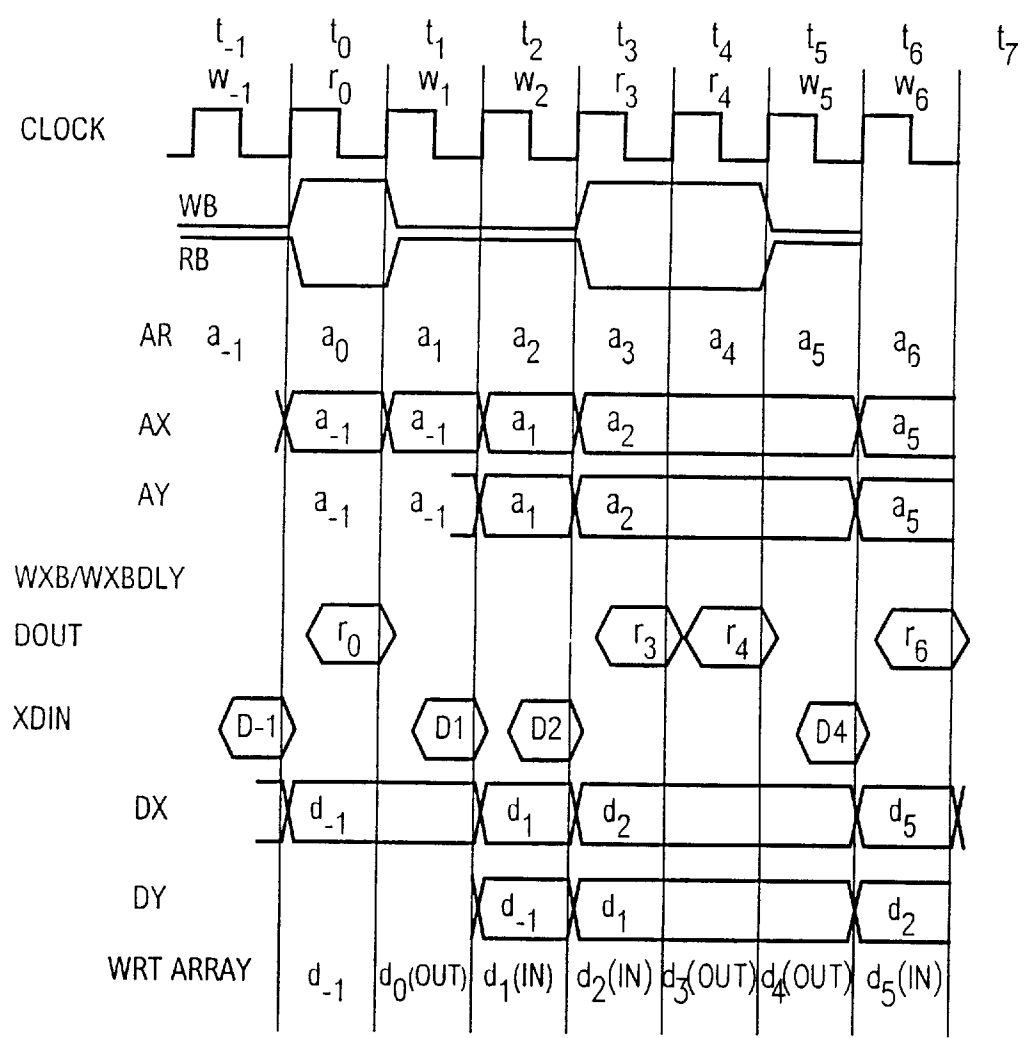e same address. In systems where bus turnaround occurs frequently, the lost cycles on bus turnaround can significantly reduce the bandwidth of the system. With conventional synchronous SRAM's, the same problem can exist.

SUMMARY

According to the present invention, a fully synchronous pipelined RAM with no lost cycles on bus turnaround is provided (i.e., the RAM is capable of performing a read operation during any clock cycle or a write operation during any clock cycle without limitation).

One embodiment of the present invention, an SRAM, includes a memory, an input circuit and a logic circuit. The

input circuit is coupled to receive a memory address and control signals during any cycle referred to as the nth cycle. During a write operation on the nth cycle, the corresponding write data to be written into the SRAM is provided during the next, (n+1)th, cycle. During the nth cycle, the logic circuit causes the previously stored write data to be written from the input circuit into the memory. The new write data associated with the address and control signal received on the nth cycle is received into the input circuit on the (n+1)th cycle. The write data and the address remain in the input circuit during any intervening read operations.

In this embodiment, when performing a read operation, the logic circuit compares the address of the read operation to the address of the most recent write operation. If the addresses match, then the SRAM outputs the data stored in the input circuit; however, if the addresses do not match, the SRAM outputs the data stored in the memory corresponding to the requested read address.

In another embodiment of the present invention, an SRAM includes an input circuit, an output circuit, a logic circuit and a memory. In this embodiment, the input circuit is coupled to receive a memory address and control signals during any cycle referred to as the nth cycle. The output circuit includes a register to store data read from the memory which is read during the (n+1)th cycle. Data will then be provided out of the output circuit on the next, (n+2)th, cycle.

The logic circuit causes the write data to be stored in a first data register in the input circuit two clock cycles after receipt of the write address and control signals. This data will move through the two-stage pipeline in the input circuit during intervening read operations. Thus, write data is written into the memory during the second write operation after the data has been received in the input circuit. These operations and their associated variations will be more fully understood in accordance with the detailed description taken with the drawings.

When performing a read operation, the logic circuit compares the address of the read operation to the addresses of the previous two write operations. If the read address matches one of the write-addresses stored in the input circuit, then the SRAM outputs to the output circuit the data corresponding to the matched address from the input circuit to the output circuit; if the read address matches both of the write-addresses stored in the input circuit, then the SRAM outputs to the output circuit the data corresponding to the most recently written matched address from the input circuit to the output circuit; however, if the addresses do not match, the SRAM outputs to the output circuit the data stored in the memory corresponding to the requested read address.

This invention will be more fully understood in accordance with the following detailed description taken with the drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 shows a block diagram of one embodiment of the present invention using a single stage pipeline.

FIG. 2 shows a more detailed diagram of the embodiment of FIG. 1.

FIG. 3 shows a timing diagram illustrating the operation of the embodiment of FIG. 2.

FIG. 4 shows a block diagram of another embodiment of the present invention using a two-stage pipeline.

FIGS. 5A, 5B and 5C show timing diagrams illustrating the operation of the embodiment of FIG. 4.

FIGS. 6A and 6B illustrate the logic states of certain components and terminals shown in FIG. 7 for two different

read/write sequences applied to the structure shown in FIG. 7 in the double pipelined (i.e., two-stage pipeline) mode.

FIG. 7 shows a schematic block diagram of an embodiment of the present invention capable of operating in either a single pipeline or two-stage pipeline configuration.

FIGS. 7A and 7B show the embodiment of FIG. 7 modified for single stage pipeline and two-stage pipeline operation, respectively.

FIGS. 8A and 8B show timing waveforms for two sequences of read/write signals applied to the structure of FIG. 7 operating in the single pipeline mode and dual pipeline mode, respectively.

FIG. 9 shows an embodiment of this invention suitable for implementation in an integrated circuit chip.

FIGS. 10A and 10B show timing waveforms illustrating the operation of the embodiment of FIG. 9 in the two-stage pipeline mode for two different sequences of read/write signals.

FIG. 10C shows timing waveforms illustrating the operation of the embodiment of FIG. 9 in the one stage pipeline mode for one sequence of read/write signals.

DETAILED DESCRIPTION

FIG. 1 shows a simplified block diagram of a single pipeline SRAM 100 according to one embodiment of the present invention. Although this embodiment utilizes SRAM memory cells, this invention also can be embodied using DRAM memory cells. SRAM 100 includes a memory 110 connected to control logic 120, which is connected to an input circuit 130. Input circuit 130 is coupled to receive address, control, and clock signals from a processor or controller (not shown) on input address bus 131, input control lead or bus 132, and input clock lead 134, respectively. Input data bus 133 is connected to control logic 120.

A read operation is performed as follows. During the nth cycle, the processor or controller (not shown) provides to SRAM 100 an address to be read on bus 131. The processor or controller also indicates a read operation by asserting (i.e. taking high) the read/write signal transmitted on control lead or bus 132. During the (n+1)th cycle, control logic 120 compares the address of the read operation stored in input circuit 130 to the address stored in control logic 120 during the most recent write operation. If the addresses match, then control logic 120 outputs the data stored in the control logic 120 corresponding to the most recent write operation via an output buffer 140; however, if the addresses do not match, control logic 120 outputs, via output port D0 and buffer 140, the data stored in SRAM memory 110 corresponding to the address of the read operation. Because the data is read from control logic 120 when a read operation sequentially follows a write operation and the address of the data to be read corresponds to the address to which the last received write data is to be written, no extra cycle is needed to write the data into memory 110 before it can be read as in conventional synchronous SRAMs. As a result, lost cycles are eliminated during bus turnaround, thereby increasing the bandwidth of a system using SRAM 100.

A write operation is performed as follows. The processor or controller (not shown) provides to SRAM 100 an address on bus 131 during an nth cycle. The processor or controller also indicates a write operation by deasserting (i.e. taking low) a read/write signal transmitted on input control lead or bus 132. Control lead 132 may be replaced by a bus which can then carry other control signals, such as a chip enable signal and a chip select signal. The processor provides on the

(n+1)th cycle the corresponding data on bus 133 (called "write data") to be written to SRAM 110 during the (n+2)th write cycle at the address on bus 131 during the nth cycle.

Input circuit 130 receives and stores the address and control on one cycle and the corresponding write data on the next following cycle. Input circuit 130 receives the address and control and input logic 120 receives the write data with a much shorter set up and hold time relative to a typical SRAM memory, thereby allowing SRAM 100 to have a shorter cycle time.

During the (n+1)th cycle, control logic circuit 120 causes the write data stored in control logic 120 during the previous write operation to be written into SRAM memory 110 and stored there at the address also stored in control logic 120 associated with that write data.

Logic circuit 120 simply holds the write data and write address during any intervening read operations.

FIG. 2 shows an embodiment of the SRAM system 100 in FIG. 1. Like reference numerals are used between drawings for like structures. SRAM system 100 includes registers A1, A3, R1 and D3. Register A3 and register D3 each includes an enable input lead 200-1 and 200-2 respectively. When register A3 or register D3 receives a logic low signal on enable input lead 200-1 or enable input lead 200-2, respectively, register A3 or register D3 will operate as a conventional register. However, register A3 and register D3 each will not alter the stored information on its output bus 205 or 221, respectively, while a logic high signal is received on enable input lead 200-1 or enable input lead 200-2, respectively.

Registers A1, R1 and D3 are respectively coupled to receive the address signals via bus 131, the read/write control signal via bus 132 and the data signals from the Data I/O input port via bus 133. The output bus 201 of register A1 is connected to the input bus 202 of register A3 and to the H input port 203 of a multiplexer 204. The output bus 205 of register A3 is connected to the L input port 206 of multiplexer 204. The output port 207 of multiplexer 204 is connected to the address port of memory 110. Thus, multiplexer 204 operates to provide either the address stored in register A1 or the address stored in register A3 to memory 110 to identify in memory 110 either the address from which read data is to be read or the address to which write data is to be written.

Multiplexer 204 is controlled by the read/write signal stored in register R1, which signal register R1 provides to the select input lead of multiplexer 204 via line 208. The stored read/write signal, when asserted (i.e. high) to indicate a read operation, causes multiplexer 204 to pass the output signals of register A1 to the address port of memory 110.

Conversely, the stored read/write signal, when deasserted (i.e. low) to mean a data-write operation, causes multiplexer 204 to pass the output signals of register A3 to the address port of memory 110; the write data signals in register D3 are already applied to the Data-In port of memory 110.

In addition, the stored read/write signal, when deasserted to indicate a write operation, enables register A3 to store the output address signals from register A1 and further enables new write data to be stored in register D3, this new write data being associated with the address signals being transferred from address register A1 to address register A3. All register storage is on the rising clock edge where the clock signal transitions from low-to-high.

FIG. 3 shows a timing diagram exemplifying a series of read and write operations. With reference to FIGS. 2 and 3, a read operation is performed as follows. In the nth cycle, the

read/write signal into register R1 is asserted (i.e. goes high) on lead **132**. Register R1 receives and stores the asserted read/write signal on the rising edge of the clock signal at the end of the nth cycle (i.e. the start of the (n+1)th cycle) and outputs the asserted read/write signal at the beginning of the (n+1)th cycle. At the same nth cycle as the read/write signal into register R1 is asserted, register A1 receives the read address on input bus **131**, and on the next rising edge of the clock signal at the start of the (n+1)th cycle, stores in, and outputs from register A1 the address a_1 to be accessed. At the same time, address a_0 stored in register A1 is transferred to register A3 since the diagram shows a write cycle at the beginning of the nth cycle. The asserted (i.e. high) read/write signal output from register R1 at the beginning of the (n+1)th cycle causes multiplexer **204** to pass address al in register A1 to memory **110**. No write data is associated with the read operation.

Assuming that the read/write signal applied on the input lead **132** to control register R1 during the (n−1)th cycle represented a write operation, then the address a_0 stored in address register A1 during the nth cycle represents the address in memory **110** to which data d_0 is to be written. Data d_0, data to be written into SRAM **110** at address a_0, is applied at the Data I/O port during the nth cycle and is stored in data register D3 on the low-to-high transition of the clock signal at the end of the nth cycle.

SRAM system **100** also includes a comparator **211** having an input bus **212** connected to output port **201** of register A1 and another input bus **213** connected to output port **205** of register A3. Consequently, during the first part of the (n+1)th cycle comparator **211** compares the requested read address a_1 (the address stored in register A1) to the address a_0 of the location in memory to which data d_0 in register D3 will be sent on the next write clock cycle (this location is at the address a_0 stored in register A3). When comparator **211** detects that addresses a_1 and a_0 match, then the read operation is reading from the address a_0 (stored in register A3) to which data d_0 in register D3 is to be written in the next write operation. The updated data d_0 stored in register D3 and corresponding to address a_0 in register A3 has not yet been written into memory **110**; rather, the updated data d_0 is passed to the input port **218** of mux **217**.

The output lead **215** of comparator **211** is connected to select lead **216** of multiplexer **217**. Multiplexer **217** has an H input port **218** connected by bus **221** to the output port **219** of register D3. Multiplexer **217** has an L input port **220** connected to the Data-Out port of memory **110**.

During the read operation in the (n+1)th cycle, if comparator **211** detects that address a_1 in register A1 does not match address a_0 in register A3, then multiplexer **217** selects the Data-Out port of memory **110** (i.e., data d_1 stored in memory **110** corresponding to address a_1) and outputs this data on bus **220** through mux **217** and through buffer **140** to the Data I/O bus. However, if comparator **211** detects that address a_1 does match address a_0 in register A3, then during the (n+1)th cycle, multiplexer **217** passes the output signals do on buses **221** and **218** from the data out port **219** of register D3 to the Data I/O bus through buffer **140**.

Referring to FIGS. **2** and **3**, a write operation is performed as follows. In this example, the read/write signal (i.e. R/W*) is deasserted (i.e. taken low) during the (n+1)th cycle to indicate a write operation is to take place in the (n+2)th cycle. On the next transition of the clock signal from low-to-high at the end of the (n+1)th cycle and the beginning of the (n+2)th cycle, register R1 receives, stores and outputs the deasserted read/write signal. Consequently, a low signal

on the select input line **208** of multiplexer **204** causes mux **204** to pass on bus **207** to the address port of SRAM **110** the output signals on bus **205** representing the address a_0 stored in register A3 (which is the address in SRAM memory **110** to which the data d_0 stored in register D3 as a result of the previous write operation during the nth cycle is to be written).

Write enable circuit **210** controls the actual writing of data into SRAM **110**. Circuit **210** is enabled by the deasserted (i.e. low) write signal as is register D3, thereby causing memory **110** to receive at the Data-In port, the data signals d_0 on buses **221** and **218** from register D3 on the next low clock signal (SRAM **110** is enabled by write enable circuit **210** to write data d_0 on the low clock signal during cycle (n+2)). During cycle (n+2) the data d_0 in register D3 will be written into the location in memory **110** defined by the address a_0 in register A3. Also, during cycle (n+2), register A1 receives, stores and outputs the address a_2 to which to-be-received data d_2 applied to the Data I/O terminal during the (n+2)th cycle is to be written in SRAM **110** on the next write cycle.

Pulse circuit **210** provides a delayed self timed high-low-high pulse after a low-to-high clock signal after waiting the required time to receive the stored deasserted read/write signal from register R1 via a line **200**. This pulse causes memory **110** to store at the address a_0 (received from register A3 via multiplexer **204**) the data d_0 received at the Data-In port of memory **110**. The Data-In port of memory **110** is connected by buses **218** and **221** to the output port **219** of register D3, which outputs data d_0 (the data from the previous write operation associated with address a_0).

In addition, during the (n+2)th cycle, data d_2 is applied to the Data I/O terminal and thus to the input port of register D3. Data d_2 corresponds to address a_2 loaded in register A1 during the low-to-high transition of the clock signal signifying the end of the (n+1)th cycle and the beginning of the (n+2)th cycle. During the (n+2)th cycle, the read/write signal is asserted (i.e. goes high) to indicate that a read operation associated with address a_3 will take place during cycle (n+3).

At the end of cycle (n+2), on the low-to-high transition of the clock signal, register D3 stores data d_2 associated with address a_2. Address a_2 in register A1 is transferred to register A3 also at the end of cycle (n+2).

In the same manner as described above, the read/write signal asserted during the end of cycle (n+2) is stored in register R1on the low-to-high transition of the clock signal at the start of cycle (n+3). Register R1 provides the asserted read/write signal on output lead **200** to disable pulse circuit **210**, on output lead **200-2** to disable data register D3 and on output lead **200-1** to disable address register A3. Thus, on the low-to-high transition of the clock signal at the start of the (n+4)th cycle, address a_2 remains in address register A3.

Then, during the cycle (n+3), the read/write signal is deasserted (i.e. goes low), thereby indicating the start of another write operation during upcoming cycle (n+4). Thus, during cycle (n+4) the output signal from register R1 is low thus enabling pulse circuit **210**. Pulse circuit **210** provides a pulse to write data d_2 from register D3 into the location in memory **110** at address a_2 in address register A3 during cycle (n+4) a delayed time after the low-high transition of the clock signal.

Referring back to cycle (n+2), during this cycle the read/write signal is asserted, thereby indicating a read operation. This read operation sequentially follows a write operation (i.e., bus turnaround), which would result in a lost cycle

7

in conventional synchronous SRAM's because the conventional synchronous SRAM must write the data into the main memory before this data can be read during the read operation. However, in memory circuit **100**, the operation of comparator **211** and multiplexer **217** provides the data requested by the read operation (specified by an address a_3 in register A1) if this data is d_2 (the address a_2 to which this data d_2 is to be written is stored in register A3 at the start of cycle (n+3)) without first writing this data d_2 into memory **110**, thereby eliminating the lost cycle. Accordingly, an SRAM memory system **100** will have higher system bandwidth relative to the conventional synchronous SRAM system because there is no lost cycle on bus turnaround.

FIG. **4** shows a block diagram of another embodiment of the present invention. In the embodiment of FIG. **4** each of the elements disclosed therein is identical to the elements disclosed in FIG. **1** with the exception that buffer **140** has been replaced by register **440**. Register **440** allows the fully synchronous SRAM of this invention to be used in the system with two pipeline delays as opposed to the single pipeline delay system shown in FIG. **1**. Thus, an output signal from SRAM **110** is passed through control logic **120** on bus **443** to register **440** and there stored to be read out of register **440** on bus **444** in response to a clocking signal brought to register **440** on leads **441** and **442** from an external clock (not shown) on the next following clock cycle. The remainder of the structure shown in FIG. **4** at the level of abstraction depicted is identical to that shown in FIG. **1** and operates in essentially the same manner as described above in conjunction with FIGS. **1**, **2** and **3** but with two cycle delays associated with data to be written into SRAM **110** and with additional registers and logic required to implement the two-stage pipeline delay.

FIGS. **5A**, **5B**, and **5C**, respectively, illustrate the double pipeline read sequence for reading information from the memory of FIG. **7**, the double pipe write sequence for writing information into the memory at a specified address, and an illustrative double pipe read and write sequence as applied over a period of clock cycles illustrated as **0–8** (FIG. **5C**).

As shown in FIG. **5A**, the double pipe read requires the presence on the input bus to the first address register of an address containing information to be read on the first cycle, the read out from the SRAM of the information at the specified address in the SRAM in the second cycle and then, on the third clock cycle, the storage of this data in a system register and the reading out from the system register of this data.

The double pipe write shown in FIG. **5B** requires the presence on the input bus to an address register of an address of the location in memory to which data is to be written on the first cycle, a delay for the second cycle during which time the address on the input bus is transferred into the address register. This is followed by a third cycle during which write data to be written into the memory is applied to the input bus of a first data register. This data is written into the first data register in the system on the fourth cycle.

FIG. **7** illustrates a fully synchronous SRAM system utilizing the principles of this invention. As a feature of this circuit, read and write cycles can be intermixed without bus turnaround cycles for a read cycle following a write cycle. Edge triggered registers (i.e. registers which load signals previously applied to their input buses on a low-to-high clock signal transition) are used to store address, data and control signals. The unique bus turnaround capability of this invention is achieved using internal edge-triggered flip flops and various gating and controlling logic.

8

In the single pipeline delay mode, read data to be output from the system is available at the Data I/O bus on the next clock cycle after the read address and control signals are presented to the input leads. A separate asynchronous output structure is available to solve high speed timing problems on read cycles should such problems arise.

Data for write cycles is presented to the Data I/O bus on the cycle following the cycle in which the address and control signals are presented to the address input bus and the control signal input bus, respectively. Thus, whether read or write, the data signals are always one cycle delayed from address and control signals. But the address and control signals are applied to the memory simultaneously in proper timing to ensure that the data is written to or read from the proper cells in the memory.

The structure shown in FIG. **7** is particularly useful in very high speed digital applications. For example, digital signal processing memories for recursive or nonrecursive filters or digital integrators can move data on every clock cycle. ATM switches can have access to data cells continuously without dead cycles. High speed cache memory systems can implement read cycles or write cycles on every clock cycle without interruption caused by the memory component. In many high speed applications, this can result in a speed improvement of up to fifty percent (50%), for example.

In the circuit block diagram schematic shown in FIG. **7**, the following abbreviations are used.

NAME	PINS	FUNCTION
Address	17 or more	Address inputs. Word select in the SRAM.
Data	8	Data inputs/outputs.
CLK	1	Clock input. All operations (except write to SRAM 710) execute on the low-to-high transitions.
R/W*	1	Read/Write input.
CS*	1	Chip select input. When active (low), the chip is enabled. When high, the chip is deselected and all functions are disabled.
CEN*	1	Clock enable input.
CpEN	1	When active (low), the chip is enabled. When not active (high), all register operations are disabled. Data still appears on the output data bus if the last valid operation was a read and data still appears on the input bus to be written into memory if the last valid operation was a write.
OE*	1	Output enable input. An asynchronous signal. When low, the output buses are enabled. When high, the output buses are high impedance.
Sgl/Dbl*	1	When high, the data in or out is delayed by one clock cycle. When low, the data in or out is delayed by two clock cycles.
Cnt/Load*	1	When low, the address register will load the address presented on the

-continued

NAME	PINS	FUNCTION
		address pins. When high, the address register will load the value currently held in the register as modified by the +1 logic; linear or other mapping.
Vdd	6	Plus voltage inputs.
Vss	7	Ground inputs.

With the above definitions of terms, the schematic block diagram shown in FIG. 7 will now be described. The SRAM system of FIG. 7 has the unique property of being able to read or write on every cycle with no dead cycles. The data, read or write, is always delayed by one or two clock cycles (a function of whether a single clock cycle delay or a two clock cycle delay is used) compared to the address and control signals.

The circuit of FIG. 7 is capable of operating either as a single pipeline structure (one clock cycle delay) or a double pipeline structure (two clock cycle delay). Thus, when the signal SGL/DBL* (denoted as S/D* in FIG. 7) is high, the data in/out is delayed by one clock cycle. When SGL/DBL* is low, the data in/out is delayed by two clock cycles.

In the schematic block diagram of FIG. 7, comparators have been given the numbers 701-i, where i represents a particular comparator, multiplexers have been given the numbers 703-i, where i represents a particular multiplexer, address registers have been given the numbers 704-i where i represents a particular address register, read/write (R/W*) control signal registers have been given the numbers 707-i where i represents a particular control signal register, chip enable registers have been numbered 708-i, and two sets of registers whose uses will be described shortly have been numbered 709-i and 710-i, where i equals 1 or 2. Inverters have been numbered 705-i and logic gates, delays, an edge detector, an output buffer and other miscellaneous components have been given the numbers 706-i. Item 702 is a pulse generator. To avoid cluttering the drawing, leads and terminals have not been numbered.

SINGLE PIPELINE OPERATION

In the single pipeline configuration (i.e. one clock delay version) of the structure of FIG. 7, S/D* is high. The operation of the structure of FIG. 7 in the single pipeline mode (i.e. single clock delay mode) will be explained in light of the timing waveforms of FIG. 8A.

While time has been shown as starting at t_0 in FIG. 8A, this choice is arbitrary. In any event, time t_0 should be understood t_0 represent some arbitrary time during the operation of the circuit and not the start time of the circuit. This is shown in FIG. 8A by the notation n, n+1, n+2, . . . n+8 placed above the arbitrary times t_0, t_1, t_2, . . . t_8, respectively to show that FIG. 8A describes the nth through (n+8)th cycles of operation, where n is a selected integer.

Period t_0

During period t_0 the address signals a_0 and the R/W* signal are supplied to appropriate input buses to the circuit. These signals are clocked into address register 704-1 and control register 707-1 on the low-to-high clock transition at the end of period t_0 and the start of period t_1. During period t_0 (and all subsequent time periods of operation of this circuit of FIG. 7) the select input signal Cnt/Load on the select input lead to mux 703-1 is low thereby allowing the address signals a_0 applied to the address input bus of mux

703-1 to pass through mux 703-1 to the D input bus of address register 704-1. Register 704-1 is enabled by CpEn* low. Simultaneously OR gate 706-1, enabled by chip select signal CS* low, allows the R/W* signal to pass through OR gate 706-1 to the D input lead into register 707-1.

Mux 703-3 has the FLIP signal applied to its gate. This FLIP signal is low because the signal S/D*, applied to one input lead of inverter 705-4 is high (indicating one clock cycle delay). The output signal from inverter 705-4 is low so long as the system is operating in the single pipeline mode. Therefore the output signal from AND gate 706-7 will be low regardless of the states of the input signals W1 and R2 on the other two input leads to AND gate 706-7.

Similarly, OR gate 706-5 receives input signals on three input leads. The first input lead is connected to the output lead of mux 703-8. Because mux 703-8 is controlled by the high S/D* signal, mux 703-8 passes the CS1* signal through the S input lead. Since CS1* is low, OR gate 706-5 will have a low input signal on the input lead connected to the output lead of mux 703-8. Chip enable signal CpEn*, applied to the middle input lead of OR gate 706-5, is also low to enable the chip containing the circuit of FIG. 7 to operate. The third input lead to OR gate 706-5 is connected to the output lead of mux 703-6. The select input lead of mux 703-6 is driven by the high S/D* signal for the single pipeline mode. The two input leads to mux 703-6 carry the R1 and R2 signals, respectively. Because the low output signal from mux 703-8 and the low CpEn* signal enable OR gate 706-5, the signal passed by mux 703-6 is transferred through OR gate 706-5 to the output lead of OR gate 706-5. This signal, depending on whether it is low or high enables or disables, respectively, data registers 709-1 and 709-2 and address registers 704-3 and 704-4. When R1 is high, the output signal from OR gate 706-5 is high and when R1 is low the output signal from OR gate 706-5 is low. R1 is low only when a write signal is stored in control register 707-1. Thus, the output signal from OR gate 706-5 enables data storage registers 709-1 and 709-2 and address registers 704-3 and 704-4 only when the R1 signal is low indicating a write.

Referring to FIG. 8A as well as FIG. 7, the particular address a_0 to which data d_0 will be written is stored in register 704-1 on the rising edge of the clock signal between time period to and time period t_1, one clock cycle before the data d_0 associated with address a_0 is applied to the Data I/O lead of the circuit.

During time period t_0, a write signal w_{-1} is shown as stored in register 707-1.

Period t_1

If the R/W* signal is a write signal (i.e. low) during time t_0, then the output lead R1 of register 707-1 will have a low level signal during period t_1. The output signal W1 from inverter 705-1 will be high during period t_1.

The output address signal a_0 at address register 704-1 is applied to the H input bus of multiplexer 703-4.

However the select input of mux 703-4 is driven by the low R1 signal from register 707-1 and therefore the address signal a_0 applied to the H input bus of mux 703-4 is not passed through mux 703-4.

On the low-to-high transition of the clock signal at start of period t_1, data d_{-1} is transferred into data register 709-1.

During period t_1, a new address a_1 is applied to the input bus to register 704-1. Simultaneously, data d_0 is applied through the Data I/O pin to the input bus to data register 709-1. Register 709-1 is enabled to receive and store data by the low write signal R1 on the Q output lead of control register 707-1 (corresponding to the signal w_0 in FIG. 8A) applied through the S input lead of mux 703-6 to one input

lead of OR gate **706-5** to produce a low enable signal on the enable input leads E of data registers **709-1** and **709-2** and address registers **704-3** and **704-4**. At the low-to-high transition of the clock signal between periods t_0 and t_1, the control signal in register **707-1** during period to is transferred to register **707-2**. The output signal on the Q output lead from register **707-2** is inverted in inverter **705-2** to yield output signal W2 which is high or low depending on the state of register **707-2**.

The address a_{-1} in register **704-1** during period t_0 is transferred to address registers **704-2** and **704-3** during the low-to-high transition of the clock signal at the start of period t_1. This latter transfer occurs through the S input bus of mux **703-2**, the select input signal to which is S/D* which is high for the single pipeline mode of operation. The states of the select inputs on muxes **703-3** and **703-4** remain as they were during period t_0.

Mux **703-3** passes the output address a_{-1} on the Q output bus from register **704-3** and on the L input bus to mux **703-3** to the L input bus of mux **703-4** (selected by signal R1 from control register **707-1** being low) and from there to the address port of memory **710**. Thus, the address of memory **710** to which data d_{-1} in data register **709-1** will be written is a_{-1}. Simultaneously, the low FLIP signal is applied to the select input lead of mux **703-5**, the output bus of which is connected to the Data-In port of memory **710**. Consequently mux **703-5** passes the data signal d_{-1} from data register **709-1** to the L input bus of mux **703-5**. Because W1 is high when R1 is low and HOLD is high (HOLD is the inverted low output signal on the Q output lead from register **710-1**, the input signal to which is low CpEn*), AND gate **706-3** is enabled. The output signal from AND gate **706-3** goes high in response to the delayed clock signal being applied to one input lead of AND gate **706-3** through delay **706-2**. This clock signal causes write enable circuit **706-4** to produce a low pulse to enable the write input to SRAM **710**. Consequently during the period t_1, the data d_{-1} is read into and stored at the location in SRAM memory **710** given by address a_{-1} because the control signal in register **707-1** during time t_0 is a write signal w_{-1}.

Period t_2

On the low-to-high transition of the clock signal at the end of period t_1 and the start of period t_2, address a_1 is entered into register **704-1** and address a_0, previously in register **704-1**, is transferred to registers **704-2** (a "don't care") and **704-3**, replacing the address a_{-1} formerly in these two registers. Simultaneously, write signal w_1 is stored in control register **707-1**. Data d_0 is transferred into data register **709-1** and data d_1 which corresponds to the address a_1 stored in address register **704-1**, is placed on the input bus to data register **709-1** from Data I/O terminal. Data d_{-1} is transferred from register **709-1** to register **709-2** (a "don't care").

During period t_2 the clock signal is transmitted through delay **706-2** and, since HOLD and W1 are both high, causes AND gate **706-3** to cause write enable circuit **706-4** to enable SRAM **710** to write into memory the data d_0 stored in data register **709-1** at the address a_0 stored in address register **704-3**. Address a_0 stored in address register **704-3** is transmitted to the address port of SRAM **710** on the L input bus of mux **703-3** and the L input bus of mux **703-4**.

Thus, by the end of period t_2, data d_0 has been placed in memory **710** at the address a_0 and data d_1, corresponding to address a_0 placed in address register **704-1** at the start of period t_2, has been placed on the input bus to data storage register **709-1**.

Period t_3

At the start of the next time period t_3, the data d_1 is transferred into data storage register **709-1** and the data d_0 previously in this data register is transferred to data register **709-2** (a "don't care"). During period t_3, data d_1 is transferred into SRAM memory **710** through the L input bus of mux **703-5** to the Data-In port of memory **710** and stored in memory **710** at the address a_1 stored in register **704-3** during the low-to-high transition of the clock signal at the start of period t_3. Address a_1 is transmitted through the L input bus of mux **703-3** and the L input bus of mux **703-4** into the address port of memory **710** to control the location to which the data d_1 in data register **709-1** is written.

Period t_4

On the low-to-high transition of the clock signal at the start of period t_4, data d_1 is transmitted into data register **709-2** (a "don't care") replacing the data d_0 previously in that register. Simultaneously control signal W3 is placed in control register **707-1** and the control signal W2 previously in register **707-1** is transferred to control register **707-2**. Thus, signals R1 and R2 remain low reflecting the write control signals stored in registers **707-1** and **707-2**, respectively. Data d_2 is transferred into data register **709-1** replacing the data d_1 simultaneously transmitted into data register **709-2**. The address a_2 previously in address register **704-1** is transferred into address registers **704-2** (a "don't care") and **704-3**. The address a_2 is transmitted through the L input bus of mux **703-3** to the L input bus of mux **703-4** to the address port of SRAM **710**. Simultaneously, data d_2 in data register **709-1** is transmitted through the low input bus of mux **703-5** to the Data-In port of SRAM **710**. Thus, data d_2 will be written to address a_2 in SRAM **710** upon the low write enable signal from enable circuit **706-4** being applied to the write enabled port of SRAM **710** during period t_4.

Address a_4 is placed on the input bus to address register **704-1** and R/W* signal r_4, denoting a read operation, is placed on the input bus to control register **707-1** during period t_4. The Q output lead of register **707-1** still carries a low level signal because write signal w_3 is stored in register **707-1** and W1 from inverter **705-1** remains high. W2 remains high because the previous low write signal w_2 is transferred into control register **707-2** causing the output signal W2 from inverter **705-2** to remain high. The R1 input signal on the S input lead to mux **703-6** remains low thereby enabling data registers **709-1** and **709-2** and address registers **704-3** and **704-4**.

Period t_5

On the low-to-high transition of the clock signal at the start of period t_5, address a_4 is transferred into address register **704-1** and address a_3 previously in this register is transferred into address registers **704-2** (a "don't care") and **704-3**. Data d_3 is passed into data register **709-1** and write signal r_4 is transferred into control register **707-1** thereby causing signal R1 to go high. Thus, the signal W1 from inverter **705-1** goes low. The write signal r_4 in control register **707-1** causes mux **703-4** to select the signals on the H input bus for transfer to the output bus connected to the address port of SRAM **710**. Thus, the address a_3 stored in address register **704-3** is not transferred to the address port of SRAM **710**. Rather, the address a_4 stored in address register **704-1** is transmitted through the H input bus of mux **703-4** to the address port of SRAM **710**.

Because a read control signal is now stored in control register **707-1**, a read operation is to be carried out during time period t_5. If the address a_4 stored in address register **704-1** does not equal the address a_3 stored in address register **704-3**, then the output signal Eq3 from comparator **701-2** will be low. Thus, mux **703-13** will be activated to pass the data out at the address a_4 in SRAM **710** through the L input bus of mux **703-13** to the S input bus of output mux **703-12**

activated by the high level signal S/D*. This output signal will then be transmitted through output buffer **706-9** to the Data I/O pin.

The signal R1 going high passes through mux **703-6** on the S input lead and then through OR gate **706-5** to cause OR gate **706-5** to produce a high level output signal thereby disabling data registers **709-1** and **709-2** and address registers **704-3** and **704-4**. Consequently, at the start of the next time period, these registers will be disabled and will retain the contents which they held during period t_5.

Should, however, the address a_4 equal the address a_3 stored in address register **704-3**, Eq3 will be high. High Eq3 will cause the data d_3 in data register **709-1** to be transmitted through the H input bus of mux **703-13** and from there to the S input bus of mux **703-12** to the output buffer **706-9** and from there to the Data I/O port. Thus, the data stored in data register **709-1** does not have to be written into SRAM **710** when address a_4 equals address a_3 but rather can be read out of the system to the Data I/O bus.

Address signal a_5 and control signal r_5 are applied to the input bus and lead, respectively, of address register **704-1** and control register **707-1**.

Period t_6

On the low-to-high transition of the clock signal at the start of time period t_6, address a_5 is loaded into address register **704-1**. Address a_4 previously in this register is transferred to address register **704-2** (a "don't care"). Address a_3 previously in address register **704-3** remains in address register **704-3**, because register **704-3** has been disabled by a high level output signal from OR gate **706-5**.

Simultaneously, read control signal r_5 is loaded into control register **707-1** and the previous read control signal r_4 in register **707-1** is transferred to register **707-2**. Thus, signal R1 is high and signal W1 is low. Because OR gate **706-5** produced a high level output signal during period t_5, data register **709-1** is disabled. Thus, throughout period t_6 data register **709-1** retains the data d_3 previously placed in that register at the start of time period t_5.

Control signal r_5 indicates that a read of the data at address a_5 is to be carried out on SRAM memory **710** during period t_6. Address a_5 from register **704-1** is transmitted through the H input bus of mux **703-4** selected by R1 being high to the address port of SRAM **710**. If address a_5 does not equal address a_4 in data register **704-2**, then the signal Eq2 from comparator **701-1** will be low. If a_5 does not equal a_3 stored in data register **704-3** the signal Eq3 will also be low. Thus, the data in SRAM **710** at address a_5 will be transmitted through the Data Out port and through the L input bus of mux **703-13** to the S input bus of mux **703-12** and from there through output buffer **706-9** to the Data I/O bus from the system.

If, however, the address a_5 equals the address a_3 stored in data register **704-3**, then the output signal Eq3 from comparator **701-2** will be high. Eq3 high will cause the data d_3 stored in data register **709-1** to be transmitted through the H input bus of mux **703-13** to the S input bus of mux **703-12** and from there through buffer **706-9** to the Data I/O port. Buffer **706-9** is enabled during period t_6 as it was during period t_5 by the high R1 output signal from control register **707-1**.

Address a_6 and control signal w_6 are applied to the input bus and input lead, respectively, of address register **704-1** and storage register **707-1**.

Period t_7

On the low-to-high transition of the clock signal at the start of period t_7, address a_6 is loaded into address register **704-1**. Address a_5 previously in address register **704-1** is

loaded into address register **704-2**. However address a_3 previously in address register **704-3** remains in address register **704-3** because this register has been disabled by the high output signal from OR gate **706-5**.

Simultaneously, write control signal w_6 is transferred into control register **707-1**. Read signal r_5 previously in control register **707-1** is transferred to control register **707-2**. Thus, the signal R1 goes low and W1 goes high enabling AND gate **706-3**.

The control signal w_6 means a write operation is now to be carried out on SRAM memory **710**. However, the last write data to be placed in data register **709-1** is data d_3. This data has yet to be written to SRAM **710**. The address a_3 to which this data d_3 should be written is still stored in address register **704-3** which has been disabled by the two high level read signals during periods t_5 and t_6. Thus, during period t_7 the address a_3 is transmitted from address register **704-3** through the L input bus to mux **703-3** to the L input bus of mux **703-4** selected by the signal R1 being low, and thus to the address port of SRAM **710**. Simultaneously, the signal d_3 in data register **709-1** is transmitted on the L input bus of mux **703-5** to the data in port of SRAM **710**. The clock signal passed through delay **706-2** and AND gate **706-3** during cycle t_7, enables data d_3 to be written into SRAM **710** to the address a_3 at the address port of SRAM **710**.

Period t_8 and subsequent periods

The system operation during period t_8 and subsequent periods will be as described above with the data to be written into or read from memory always appearing on the Data I/O bus one cycle after the address to which this data is to be written or from which it is to be read, appears on the input bus to the address register **704-1**.

Thus, the system operates to eliminate the one cycle delay during the reading of data from the memory caused by the need to store in the memory the data to be written into the memory before the same data can be read from the memory during a read operation immediately following a write operation.

FIG. **7A** illustrates the structure of FIG. **7** where all unnecessary elements in the logic block diagram of FIG. **7** have been removed to implement the single pipeline operation of the structure of FIG. **7**. The operation of the structure of FIG. **7A** is as described above in conjunction with FIG. **7**.

DOUBLE PIPELINE OPERATION

The double pipeline operation is characterized by S/D* going low. Thus, the signal FLIP from AND gate **706-7** will be high or low depending on the states of signals W1 and R2. Contrary to the single pipeline operation described above, where the signal FLIP was always low because the signal S/D* was always high, FLIP will change from high to low depending on the states of the control signals in control registers **707-1** and **707-2**.

Also, as with FIG. **8A**, while the time periods in FIG. **8B** are shown as starting at time t_0, this choice is arbitrary and for convenience only. Time t_0 represents some arbitrary time (characterized as the nth cycle) during the operation of the circuit and not the start time of the circuit. As with FIG. **8A**, times $t_1, t_2, \ldots t_8$ correspond to cycles n+1, n+2, . . . n+8 where n is an arbitrary integer.

Period t_0

Referring to FIGS. **7** and **8B**, during period t_0, address a_0 is applied to the input bus to address register **704-1**. Simultaneously a read control signal r_0 is applied to the input lead of control register **707-1**. The signal S/D* is low. Accordingly, an input signal on the D* input bus to mux

703-2 is passed to the output bus of mux **703-2**. The output bus of mux **703-2** is connected to the D input bus of address register **704-3**.

Period t_1

On the low-to-high transition of the clock signal CK at the start of period t_1, address signal a_0 is transferred into address register **704-1**. Simultaneously address a_{-1}, already in address register **704-1**, is transferred to address register **704-2**. At the same time, the read control signal R/W*, shown in FIG. **8B** as r_0, on the input lead to control register **707-1**, is transferred into control register **707-1**. The write control signal w_{-1} in control register **707-1** during period to is transferred to control register **707-2**. Thus, the R1 and R2 signals are high and low, respectively, and the W1 and W2 signals are low and high, respectively. During period t_1, because the signal W1 is low and the signal R2 is low, even through the D input signal to AND gate **706-7** is high, the signal FLIP is low.

The low S/D* signal causes mux **703-2** to transmit the address a_{-1} in register **704-2** on output bus Q to the D* input bus of mux **703-2** and through mux **703-2** to the D input bus of address register **704-3**.

The control signal r_0 is stored in register **707-1**. The control signal r_0 is high meaning that information is to be read from SRAM **710** during time period t_1. To do this, the address signal a_0 in address register **704-1** is applied to the H input bus of mux **703-4**. Mux **703-4** has the high level signal R1 on its select input lead and thus passes address a_0 to the address port of SRAM **710**. The data stored at the location in SRAM **710** given by address a_0 is then passed to the Data Out port of SRAM **710** and to the low input bus of mux **703-7**. Mux **703-7** passes this data to the low input bus of mux **703-9** which in turn passes this data to the low input bus of mux **703-11**. The select inputs of muxes **703-7** and **703-9** both have low signals thereby activating their low input buses. The output signal from AND gate **706-6** is low because Eq2 is low meaning comparator **701-1** produces a low output signal. Thus, mux **703-11** passes the data being read out of SRAM **710** to the D input bus of output register **710-2**. This data is then read into register **710-2** on the low-to-high transition of the clock signal at the end of period t_1 and the start of period t_2. Thus, during period t_2 the data being read out of SRAM **710** will be applied to the D input bus of mux **703-12** and from this D input bus to the output bus from mux **703-12** (S/D* is low thereby enabling this path). Because during period t_2 the signal R2 will be high, this data will be passed during period t_2 from buffer **706-9** (enabled by a high output signal from AND gate **706-8** reflecting the high level signal R2) to the Data I/O terminal from which this data will be sent to its destination.

Address signal a_1 and read control signal r_1 are applied to the input bus and input lead, respectively, of address register **704-1** and control register **707-1**.

Period t_2

At the start of period t_2, the low-to-high transition of the clock signal causes the address a_1 applied to the input bus of address register **704-1** to be stored in address register **704-1**. Simultaneously, the address a_0 previously stored in address register **704-1** is stored in address register **704-2**. The control signal r_1 indicating that the information stored at address a_1 is to be read out of SRAM **710**, is read into control register **707-1**. The control signal r_0 previously in register **707-1** is read into control register **707-2**. Thus, the signals W1 and W2 are both low and the signals R1 and R2 are both high. The data d_0 read out from SRAM **710** during period t_1 and placed on the input bus D to output register **710-2** is transferred into output register **710-2** and transferred on the

Q output bus from register **710-2** to the D input bus of mux **703-12**. As described above under period t_1, this data d_0 is then passed from the D input bus of mux **703-12** through mux **703-12** enabled by the S/D* signal being low, to and through output buffer **706-9** enabled by the high level output signal from AND gate **706-8**. The data d_0 being output from the memory is passed through buffer **706-9** to the Data I/O port and sent from there to its destination.

Simultaneously, the address a_1 in register **704-1** is passed to the H input bus of mux **703-4**. Because the select input of mux **703-4** is driven high by signal R1, this address a_1 is passed to the address port of SRAM **710**. The information d_1 located in SRAM **710** at address a_1 is then passed through the Data Out port from SRAM **710** to the L input bus of mux **703-7** and through mux **703-7** to the L input bus of mux **703-9**. Both muxes **703-7** and **703-9** have low input signals on their select inputs and thus pass this data d_1 to the L input bus of mux **703-11**. This mux also has a low input signal on its select lead and thus passes the data d_1 through mux **703-11** to the D input bus of register **710-2**.

Address signal a_2 is applied to the input bus of address register **704-1** while write control signal w_2 is applied to the input lead of control register **707-1**.

Period t_3

At the low-to-high clock transition at the start of period t_3 the address a_2 which has previously been placed on the input bus to address register **704-1** during period t_2, is loaded into address register **704-1**. Simultaneously, the control signal w_2 applied to the D input lead of control register **707-1** is loaded into control register **707-1**. The signal r_1 previously in control register **707-1** is loaded into control register **707-2**. Thus, the signals W1 and W2 become high and low, respectively, and the signals R1 and R2 become low and high, respectively. At the low-to-high clock transition at the start of time t_3, the data d_1 on the D input bus to register **710-2** (read out from the address location a_1 during the previous period t_2) is transferred into register **710-2** and made available through mux **703-12** and output buffer **706-9** to the Data I/O port.

Address signal a_3 and write control signal w_3 are applied to the input bus and input lead, respectively, of address register **704-1** and control register **707-1**.

Period t_4

The control signal w_2 in register **707-1** during period t_3 means that in period t_4 data d_2 will be applied to the Data I/O bus and to the D input bus of register **709-1**. This data d_2 will be written into SRAM **710** at the address given by w_2 during a subsequent write period.

On the low-to-high transition of the clock signal at the start of period t_4, the write control signal w_3 is placed in register **707-1** and the address a_2 specifying the location in memory **710** at which data d_2 is to be stored is transferred from address register **704-1** to address register **704-2**. The control signal w_2 is transferred from control register **707-1** to control register **707-2**. During this period, read signal r_4 is applied to the input terminal of control register **707-1** and the address signal a_4 is applied to the input bus of address register **704-1**. During this period, the data d_2 is applied to the Data I/O bus and to the D input bus of data register **709-1**.

Period t_5

On the low-to-high transition of the clock signal at the start of period t_5, the control signal r_4 is stored in control register **707-1**, address a_4 is stored in address register **704-1** and data d_2 is stored in data register **709-1**. Output signal R1 from register **707-1** is high. Output signal W1 from inverter **705-1** is low. Control register **707-2** stores the write

signal w_3. Thus, output signal W2 from inverter **705-2** is high because w_3 is low. However, the output signal from mux **703-6** remains low because the signal R2 is low. Data registers **709-1** and **709-2** along with address registers **704-3** and **704-4** are disabled. In addition, AND gate **706-3** is disabled when signal W1 goes low thereby preventing information from being written into SRAM **710**. Data d_3 is applied to the Data I/O bus; data d_3 corresponds to address a_3 applied two cycle previously to the input bus of address register **704-1**.

The address a_4 stored in address register **704-1** depicts the location in SRAM **710** at which information d_4 is to be read out from SRAM **710**. Because R1 is high, this address is supplied directly through the H input bus of mux **703-4** to the address port of SRAM **710**. Simultaneously, this address a_4 is compared in comparator **701-1** to the address a_3 stored in register **704-2** and also in comparator **701-2** to the address a_2 stored in address register **704-3**. Should the address a_3 stored in address register **704-2** equal the address a_4 stored in address register **704-1**, then Eq2 goes high. When Eq2 goes high, AND gate **706-6** produces a high output signal enabling mux **703-11**. Data d_3 on the input Data I/O bus (corresponding to data d_4 to be read out of memory **710**) is passed through mux **703-11** to the D input bus of register **710-2**. If Eq3 goes high indicating address a_2 matches address a_4, then data d_2 stored in register **709-1** (corresponding to data d_4 to be read out of memory **710**) is transmitted to the H input bus of mux **703-9** enabled by Eq3 being high, and through mux **703-9** to the low input bus of mux **703-11** (enabled by Eq2 low causing the output signal of AND gate **706-6** to be low) and to the D input bus of register **710-2**.

Address signal a_5 and read control signal r_5 are applied to the input bus and input lead, respectively, of address register **704-1** and control register **707-1**. Data d_3 is applied to the Data I/O bus.

Period t_6

At the end of period t_5 and the beginning of period t_6, address a_5 on the input bus to address register **704-1** is transferred into register **704-1** on the low-to-high transition of the clock signal. Address a_5 is then applied to the input bus of address register **704-2**. During period t_5, a read signal r_5 was applied to the input lead of control register **707-1**. This read signal r_5 is then transferred into control register **707-1** on the low-to-high transition of the clock signal at the beginning of period t_6. The read control signal r_4 in control register **707-1** is transferred to register **707-2**. Thus, both signals W_1 and W2 go low. Data d_3 is transferred into data register **709-1** and data d_2 is transferred from register **709-1** into data register **709-2** on the low-to-high transition of the clock signal.

Address register **704-3**, however, has been enabled by the low level signal from OR gate **706-5** generated by R2 being low during period t_5. Accordingly, the address a_3 on the input bus to address register **704-3** during period t_5 is transferred to address register **704-3** at the beginning of period t_6 and the address a_2 on the input bus to address register **704-4** during period t_5 is transferred to address register **704-4** at the beginning of period t_6.

A read operation is to take place during time period t_6. The information stored in SRAM **710** at address a_5 is to be read from the system.

Should the address a_5 not equal the address a_3 stored in register **704-3** or the address a_4 stored in register **704-2**, then the address a_5, transmitted to the H input bus of mux **703-4** and from there to the address port of SRAM **710**, will determine the address within SRAM **710** at which the

information d_5, to be read from the memory, is located. This information, d_5, will then be read out of SRAM **710** through the Data Out port and through the L input bus of mux **703-7**, the L input bus of mux **703-9**, the L input bus of mux **703-11** to the input bus of register **710-2**. This data d_5 will be transferred into register **710-2** on the low-to-high clock transition at the start of period t_7. Note that the comparators **701-1**, **701-2** and **701-3** all produce low output signals Eq2, Eq3 and Eq4, respectively.

If, however, address a_5 in address register **704-1** equals address a_3 in address register **704-3**, then, comparator **701-2** produces a high level output signal Eq3. A high level signal Eq3 indicates that the data d_5 to be read out from the memory system is stored in data register **709-1**. This data is read out from register **709-1** through the H input bus of mux **703-9**, the L input bus of mux **703-11**, to the D input bus of register **710-2** and is stored in register **710-2** on the low-to-high transition of the clock signal at the start of period t_7.

If the address a_5 in register **704-1** equals the address a_4 stored in register **704-2**, then the signal Eq2 goes high. However, the address a_4 does not correspond to data being read into the system but rather corresponds to a read signal r_4. Accordingly, no data is present in storage register **709-1** or **709-2** corresponding to the address a_4 and the address a_5 is transmitted directly to the address input port of SRAM **710** through the H input bus of mux **703-4**.

Thus, in both periods t_5 and t_6, which correspond to read operations, the data d_3 stored in data register **709-1** during period t_6, identified by the address a_3 in address register **704-3** during period t_6 and by the address a_3 in address register **704-2** during period t_5, is read directly out of data register **709-1** when the address stored in address register **704-1** matches the address stored in address register **704-3**. The data d_3 is read from the Data I/O bus when the address a_4 stored in register **704-1** matches the address a_3 stored in register **704-2** during period t_5.

The address signal a_6 and write control signal w_6 are applied to the input bus and input lead, respectively, of address register **704-1** and control register **707-1**. Data d_4 corresponding to the information at or to be placed at address a_4 in memory **710** is placed on the Data I/O.

Period t_7

On the low-to-high transition of the clock signal CK at the start of period t_7, address a_6,located on the input bus to address register **704-1** during period t_6, is transferred into and stored in address register **704-1**. Simultaneously, the address a_5 previously stored in address register **704-1** is transferred to address register **704-2**. During period t_6, R2 was high. Thus, data registers **709-1** and **709-2** and address registers **704-3** and **704-4** were disabled. These registers are also disabled during time period t_7. Consequently, the data d_3 in data register **709-1** and the data d_2 in data register **709-2** during period t_6 remain in place in these registers on the low-to-high clock signal transition at the start of period t_7. In addition, the addresses a_3 and a_2 in address registers **704-3** and **704-4**, respectively, likewise remain in place. Thus, during period t_7, write signal w_6 is stored in control register **707-1** while read signal r_5 is stored in control register **707-2**. Thus, a write operation is to take place and the data to be written into SRAM **710** is the data d_2 associated with the address a_2 stored in address register **704-4**. This data d_2 is stored in register **709-2**. Because both R2 and W1 are high, the FLIP signal from AND gate **706-7** is high. Thus, mux **703-5** provides the data from the Q output bus of data register **709-2** through the H input bus of mux **703-5** to the Data In port of SRAM **710**. Meanwhile the address a_2 stored in register **704-4** is provided through the H

input bus of mux **703-3** to the L input bus of mux **703-4** to the address port of SRAM **710**. The L input bus of mux **703-4** is activated by the low level signal R1on the select input of mux **703-4**.

As shown in FIG. **8B**, a write signal w_6 had been applied to the input lead of control register **707-1** during period t_6. This write signal w_6 is now stored in control register **707-1**. Thus, output signal R1 goes low causing signal W1 to go high. R2 is still high thereby still disabling data registers **709-1** and **709-2** and address registers **704-3** and **704-4**. Because address register **704-3** had previously been disabled during period t_6, the address a_5 on the input bus to address register **704-3** is not stored in address register **704-3**. Rather, address a_3 previously in address register **704-3** during period t_6 remains stored in this register. Data d_3 likewise remains stored in data register **709-1** for the same reason. The signal W1 goes high on the low-to-high clock transition at the beginning of period t_7, thereby causing AND gate **706-3** to produce a high output signal which enables write circuit **706-4** to cause the writing of information into SRAM **710** when the clock signal goes high to enable circuit **706-4** during period t_7. Thus, during period t_7, a write signal is generated by write enable circuit **706-4** which causes the data d_2 stored in data register **709-2** to be transmitted through the H input bus of mux **703-5** to the Data In port of SRAM **710** and stored at the address a_2 applied to the address port of SRAM **710** through the L input bus of mux **703-4** and the H input bus of mux **703-3** from the Q output bus of address register **704-4**.

Address signal a_7 and write control signal w_7 are applied to the input bus and input lead, respectively, of address register **704-1** and control register **707-1**.

Period t_8

On the low-to-high transition of the clock signal at the start of period t_8, address a_7 on the input bus of register **704-1** is stored in register **704-1**. Address a_6 in register **704-1** during period t_7 is transferred to and stored in register **704-2**. Registers **704-3** and **704-4**, however, are still disabled by the high level signal R2 transmitted through OR gate **706-5**. Therefore, registers **704-3** and **704-4** continue to hold the addresses a_3 and a_2, respectively. The data in data registers **709-1** and **709-2** likewise remains d_3 and d_2 respectively. The signal w_7 on the input lead to control register **707-1** during period t_7 is transferred into control register **707-1**. Signal w_6, previously in control register **707-1**, is transferred to control register **707-2**. The signals R1 and R2 become low. Consequently, the FLIP signal from AND gate **706-7** changes from high to low and thereby enables the L input bus of mux **703-5**. Consequently, the data d_3 in data register **709-1** is transferred through the L input bus of mux **703-5** to the Data In port of SRAM **710**. Simultaneously, the address a_3 stored in address register **704-3** is transmitted through the L input bus of mux **703-3** to the L input bus of mux **703-4** thereby to the address port of SRAM **710**. Consequently, the data d_3 is stored in SRAM **710** at the address a_3 during period t_8.

As can be seen from the above description, in the dual pipeline version of the invention, data to be written into the memory is applied to the Data I/O two clock periods after the write signal associated with that data is applied to the control circuit. Thus, a read signal immediately following a write signal occurs before the data associated with that write signal even appears on the Data I/O port. The data read out from the SRAM memory during the next cycle will be stored in a register prior to being transmitted on the second following clock cycle to the Data I/O port. Thus, the Data I/O port will at all times either have input data being

transmitted into the system or output data being transmitted from the system. The system basically allows data being written into the system to be held in suspense during the reading out of data from the system. The reading out of data from the system causes the addresses of the two sets of data being written into the system but still in the double pipeline to be checked to determine if the data being read out is one of these two pieces of data. If it is, the system automatically reads out the correct data from a temporary storage register; if it is not, the system automatically reads out the correct data from SRAM **710**.

FIG. **7B** illustrates the components of FIG. **7** which are required to implement the double pipeline version of this invention. The operation of the structure in FIG. **7B** is as described above in connection with the double pipeline operation of the structure shown in FIG. **7**. The elements in FIG. **7B** are numbered identically to the corresponding elements in FIG. **7**.

INTEGRATED CIRCUIT EMBODIMENT

FIG. **9** shows the structure of this invention as implemented in the preferred embodiment incorporated in a semiconductor integrated circuit chip. The waveforms shown in FIGS. **10A** and **10B** illustrate the operation of the embodiment of this invention shown in FIG. **9** in the dual pipeline mode for two sequences of operations. In FIG. **10A** the sequence of read read write write read read write write read read is described. In FIG. **10B** the sequence of read write read write read write read read is described. Naturally, in operation, any sequence of read and write signals can be applied to the circuit. The waveforms shown in FIGS. **10A** and **10B** are merely illustrative of two possible sequences of such read and write signals.

Turning to FIG. **9**, the signals depicted in FIG. **9** are as follows:

XENB=Enable signal (Low to enable)

XADDR=Address

CLK=Clock

S/DB=Single Pipeline (high)/Double Pipeline (low)

XWEB=Write (low)/Read (high)

XIO=Data signals, Input/output

XCSB=Chip Select—Low to Select

EQX=Comparator—last address-Ax to AR

EQY=Comparator—Second to last address AY to AR

DX=Last data received

DY=Second to last data received

XOEB=Output buffer enable signal

AX=Address in register **804-2**

AY=Address in register **804-3**

WXB=Output signal from control register **807-2**

Dout=Data out from memory array **810**

XDin=Data In to System

WB=output signal from register **807-1**

RB=Inverted output signal from register **807-1**

XENB is low to enable operation of the system.

Time Period t_0

At the beginning of time t_0 (an arbitrary time during the operation of the system picked solely for illustrative purposes), on the low-to-high transition of the clock signal, the address a_0 is transferred into the address register **804-1**. Simultaneously, the control signal XWEB, corresponding to a read, is transferred into control register **807-1**. The chip select signal XCSB (not shown in FIG. **10A**), which is low

to select a particular chip, is applied to the D input lead of and is thus stored in register **808-1**. The output signal CSB from register **808-1** is passed to one input lead of OR gate **805-4** and thus CSB when low enables this OR gate to pass the Q output signal from register **807-1**. CSB is also passed through inverter **812-1** which, when CSB is low, produces a high level signal CS which enables the NAND gate **805-3**. Thus, the signal RB output from NAND gate **805-3** is the complement of signal WB from OR gate **805-4**. Because at the start of time period t_0 a read control signal is transferred into the system, address a_0 in memory array **810** is applied through the H input bus of mux **803-2** (selected because WB is high to indicate a read operation is taking place) to the address port of memory array **810**. The data in memory array **810** at address a_0 is then placed on the output bus OUT from memory array **810** and then transmitted through a buffer **812-3** to the input bus to data register **811-1**. This data is then stored in register **711-1** on the low-to-high transition of the clock signal at the end of period t_0 and the beginning of period t_1.

Time Period t_1

During period t_1 a write signal w_1 has been applied to control register **807-1** and the read signal r_0 previously in control register **807-1** is transmitted through OR gate **805-4** to control register **807-2**. Signal CSB remains low as it will during all operations. Thus, the signal WXB represents the control signal in register **807-1** during the preceding time period t_0 whereas the signal WB represents the control signal in register **807-1** during the current time period t_1. Because during period t_1 a write operation is being called for, the address a_1 stored in register **804-1** represents the address to which data d_1, to be applied to the XIO pin in the next clock cycle after the address a_1 is stored in register **804-1**, is to be stored in memory array **810**. This data d_1 will be transmitted into data register **809-1** two cycles after the address a_1 is transferred into register **804-1**.

The data stored in register **811-1** during time period t_1 is transmitted through the L input bus of mux **803-5**, enabled by the low level S/DB signal, to output buffer **812-4** and from there to the XIO bus of the system. Buffer **812-4** is enabled by a high level signal from AND gate **805-10**. Gate **805-10** is enabled by the high level signal WXB stored in register **807-2** and the high level signal CSX from mux **803-3**. The high level signal CSX reflects the high level output signal from inverter **812-1** during time period t_0 stored in register **808-2** on the low-to-high transition of the clock signal at the start of period t_1. This high level signal is passed through the L bus of mux **803-3** to become the CSX output signal from mux **803-3**.

Time Period t_2

During time period t_2, a write operation is also called for. Thus, on the low-to-high transition of the clock signal at the start of period t_2, write signal w_2 is transferred into control register **807-1** and the write signal w_1 previously in control register **807-1** is transferred into control register **807-2**. Accordingly, WB and WXB become low level signals. The address a_2 is stored in address register **804-1** and the address a_1 previously stored in address register **804-1** is transferred to address register **804-2**. Data d_1 is applied to the input data bus XIO and will be transferred into data register **809-1** on the low-to-high transition of the clock signal at the start of the next time period t_3.

Time Period t_3

At the low-to-high transition of the clock signal at the start of time period t_3, the data d_1 on the input bus XIO is transmitted into data register **809-1**. Also at approximately the same time a new address a_3 is placed in address register

804-1 and the address a_2 previously in register **804-1** is transferred to address register **804-2**. The address a_1 previously in address register **804-2** is transferred to address register **804-3**. The read signal r_3 is transferred into control register **807-1** and the write signal w_2 previously in control register **807-1** during period t_2 is transferred into register **807-2**.

The address signal a_3 stored in register **804-1** is transmitted through the H input bus of mux **803-2**, selected by signal WB being high, to the address port of memory array **810**. Because a read operation is being called for, if address a_3 stored in address register **804-1** equals the address a_2 stored in address register **804-2** or the address a_1 stored in address register is **804-3**, then comparator **801-1** will produce a high output signal EQX or comparator **801-2** will produce a high output signal EQY, respectively. If address a_3 equals address a_1 then the high level signal EQY passed through inverter **812-2** causes NAND gate **805-6** to produce a low level signal thereby disabling buffer **812-3**. Thus, no output signal will be transmitted from memory array **810** to the output register **811-1**. However, because EQY is high, EQX is low, and WXB is low, the output signal of AND gate **805-9** is high and the output signal of OR gate **805-8** is high thereby enabling buffer **812-6** to pass data d_1 (DX, the last data received) from register **809-1**, to the input bus to output register **811-1**. Thus, the data d_1 stored in data register **809-1** will be stored in output register **811-1** on the low-to-high transition of the clock signal at the start of time period t_4.

If address a_3 equals address a_2, then the high level signal EQX passed through inverter **812-5** causes NAND gate **805-6** to produce a low level signal thereby disabling buffer **812-3**. Thus, no output signal will be transmitted from memory array **810** to the output register **811-1**. However, because EQX is high and WXB is low, reflecting the fact that a write signal w_2 was stored in control register **807-1** during time period t_2 and is stored in register **807-2** during time period t_3, AND gate **805-12** produces a high level output signal enabling buffer **812-12** to pass the data d_2 on the input bus XIO to the system corresponding to address a_2 in register **804-2** to output register **811-1**. Thus, the data d_2 is passed to the input bus of output register **811-1** to be stored in this register on the low-to-high transition of the clock signal at the start of period t_4.

Time Period t_4

During time period t_4, read signal r_4 is stored in control register **807-1** and previous read signal r_3 is stored in control register **807-2**. Simultaneously, on the low-to-high transition of the clock signal at the start of period t_4, address a_4 is stored in address register **804-1**. Data d_1 stored in data register **809-1** is transferred to data register **809-2** and data d_2 on the XIO input bus is transferred into data register **809-1**. Because the signal WB passed through OR gate **805-1** is high at the end of time period t_3 and also at the start of time period t_4, address registers **804-2** and **804-3** are disabled and thus retain the addresses a_2 and a_1, respectively. The address a_4 is compared to the addresses stored in address registers **804-2** and **804-3**, respectively. If the address a_4 equals the address a_2 stored in address register **804-2** or the address a_1 stored in address register **804-3** then the signal EQX or EQY, respectively will be high. If EQY is high, then EQX will be low and the address a_1 stored in address register **804-3** corresponds to the data d_1 stored in data register **809-2**. Signal WXB is now high level reflecting the storage of the signal r_3 in control register **807-2**. Consequently, AND gate **805-11** produces a high level output signal which enables buffer **812-10** to pass the data d_1 represented by signal DY, stored in data register **809-2**, to

the input bus of output register **811-1**. Data d_1 will be stored in output register **811-1** on the low-to-high clock transition of the clock signal at the start of time period t_5.

Time Period t_5

During time period t_5, data in register **811-1** will be passed through the L input bus of mux **803-5** (selected by signal S/DB being low) to output buffer **812-4** and from there to the Data I/O pin XIO to be sent outside the system.

During time period t_5 a write signal w_5 is stored in control register **807-1** and the read signal r_4 previously in this control register is transferred to and stored in control register **807-2**. Address a_5 is stored in address register **804-1** but address registers **804-2** and **804-3** continue to store addresses a_2 and a_1, respectively because these two registers are still disabled by the read signal r_4 at the low-to-high transition of the clock signal at the start of time period t_5.

Because this is a write operation, the data d_1 in data register **809-2** is to be written into memory array **810** at the address a_1 stored in address register **804-3**. The system writes data into memory array **810** on the second write operation after the address to which the data is to be written is stored in address register **804-1**. Signal WB is low therefore the mux **803-2** passes the address a_1 in address register **804-3** directly to the L input bus of mux **803-2** to the address port of memory **810**. Simultaneously, the data DY stored in data register **809-2** is applied through the H input bus of mux **803-7** selected by the high signal WXB from control register **807-2** passed through the L input bus of mux **803-6** (selected by the low S/DB signal) to the L input bus of mux **803-8** (also selected by the low S/DB signal) to the select input lead of mux **803-7**. Thus, the data d_1, represented in FIGS. **9** and **10A** by the signal DY, is passed through the H input bus of mux **803-7** to the Data In port of memory array **810** and stored in memory array **810** at the location given by address a_1 in register **804-3**.

Time Period t_6

On the low-to-high transition of the clock signal at the start of time period t_6, address a_6 is placed in address register **804-1** and address a_5 previously in this register is transmitted to address register **804-2**.

Address a_2 previously in address register **804-2** is transferred to address register **804-3**. Control signal w_6, a write signal (low), is transferred into control register **807-1** and control signal w_5, also a write signal (low), is transferred from control register **807-1** to control register **807-2**. Data d_1 remains in register **809-2** and data d_2 remains in register **809-1** because these registers are disabled by the high level signal WXB from control register **807-2** passed to the L input bus of mux **803-6** and from there through OR gate **805-5** (enabled by the low XENB signal) to disable data registers **809-1** and **809-2**.

A write operation is to take place during time period t_6. This write operation involves the transfer of the data d_2 in data register **809-1** into SRAM **810** at the address a_2 now stored in address register **804-3**. Because WB is low reflecting the write signal w_6 stored in control register **807-1**, the address a_2 is transmitted from address register **804-3** through the L input bus of mux **803-2** to the address port of memory array **810**.

Data d_2, however, is stored in data register **809-1**. The data d_2 in data register **809-1** is transmitted through the L input bus of mux **803-7** selected by the low output signal from mux **803-8** transmitted from the WXB output lead of control register **807-2** through the L input bus of mux **803-6** to the L input bus of mux **803-8** to the select input lead of mux **803-7**. The low signal WXB (note that WXB goes low during period t_6 because write signal w_5 is transmitted into

register **807-2** during period t_6) thus ensures that the data d_2 is passed through mux **803-7** from data register **809-1** to the Data In port of memory array **810** and placed at the location in memory array **810** given by address a_2 during period t_6.

Data d_5, corresponding to address a_5, is placed on the input bus XIO.

Time Period t_7

At the low-to-high transition of the clock signal at the start of period t_7, address signal a_7 is stored in address register **804-1**. Addresses a_6 and a_5 are transferred to address registers **804-2** and **804-3**, respectively. Read signal r_7 is transmitted into and stored in the control register **807-1** and the write signal w_6 previously in register **807-1** is transferred into and stored in register **807-2**. Data d_5 corresponding to the write address a_5 received and stored in address register **804-1** during period t_5, is stored in data register **809-1** and the data d_2 previously stored in register **809-1** is transferred to and stored in register **809-2**. WXB is low and thus data registers **809-1** and **809-2** are enabled. Because a read operation is being carried out during period t_7, the data stored in memory array **810** at address a_7 is to be read out of the memory array. However, if this data corresponds to the data at the address a_6 stored in address register **804-2** or to the data at the address a_5 stored in address register **804-3**, EQX or EQY from comparator **801-1** or comparator **801-2** will be high, respectively. Under these circumstances, the data d_5 stored in data register **809-1** or the data d_6 applied to the Data I/O port (shown as signal XIO) will be selected to be transferred to the input bus to storage register **811-1**. If the data d_6 is selected, reflecting the high level EQX signal, then WXB, which is low, will be inverted by inverter **812-13** and applied to one input lead of AND gate **805-12**. The high level signal EQX will be applied to the other input lead of AND gate **805-12** causing AND gate **805-12** to produce a high level output signal which enables buffer **812-12**. Buffer **812-12** transmits the data signal d_6 on the input I/O bus directly to the input bus to register **811-1** to be stored in register **811-1** on the low-to-high transition of the clock signal at the start of the next time period t_8. Thus, during period t_8, the data d_6 stored in register **811-1** will be read out of register **811-1** through the L input bus of mux **803-5** and through the output buffer **812-4** (enabled by WXB and CSX both high and XOEB low) to the I/O output bus. The circuit continues to operate as described above as additional read and write signals are applied to the circuit.

FIG. **10B** illustrates the operation of the circuit of FIG. **9** for the sequence of control signals read, write, read, write, read, write, read, read.

Time Period t_0

At time t_0 (t_0 is a time arbitrarily selected during the operation of the system), the address signal a_0 is loaded into address register **804-1**. A high level signal XWEB corresponding to a read r_0 is loaded into control register **807-1**.

Time Period t_1

At the low-to-high transition of the clock signal at the start of period t_1, address a_1 is loaded into address register **804-1**. Because the signal WB is still high, reflecting the read control signal r_0 in control **807-1** during time period t_0, OR gate **805-1** produces a high output signal disabling address registers **804-2** and **804-3**. Therefore the address a_0 in register **804-1** is essentially lost and replaced with address a_1. The control signal w_1, a low write signal, is read into control register **807-1** causing the signal WB to become low and the signal RB output from NAND gate **805-3** to become high. The write signal w_1 indicates that data d_1 is going to be applied to XIO, the Data I/O terminal, sometime during the next clock period and will be written into the data

25

register **809-1** during the second following clock period. Meanwhile any data d_0 being read out of the system as a result of the read control signal during period t_0 is transferred into output register **811-1** on the low-to-high transition of the clock signal at the start of the time period t_1. This data d_0, the data at address a_0 in memory array **810**, is transferred through buffer **812-3** enabled by EQY and EQX both being low thereby causing the output signal from AND gate **805-6** to be high and thus enable buffer **812-3**. From register **811-1**, this data d_0 is transmitted on the L input bus of mux **83-5**, through buffer **812-4**, to the Data I/O.

Time Period t_2

On the low-to-high transition of the clock signal at the start of period t_2, address a_2 is read into address register **804-1**. Address a_1 previously in address register **804-1** is transferred into address register **804-2**, enabled by the low write signal WB during time period t_1. Any address in address register **804-2** is also transferred through mux **803-1** to address register **804-3** during the same low-to-high transition of the clock signal. The read signal r_2 is transferred into control register **807-1** and the low level write signal w_1 previously in control register **807-1** during time period t_1 is transferred to control register **807-2**. Therefore WXB, the output signal from control register **807-2** is low during time period t_2. Because the operation during time period t_2 is a read, information contained at address a_2 in SRAM memory **810** is transferred to the data output of memory array **810** and through enabled buffer **812-3** to the input port of register **811-1**. If, however, the address a_2 stored in address register **804-1** of the information to be read from the memory system is equal to the address a_1 stored in address register **804-2**, comparator **804-1** produces a high level signal EQX. High level signal EQX disables buffer **812-3** and means that the data d_1 being applied to the input bus XIO during time period t_2 must also be transferred to the input bus of the output register **811-1** because this is the data to be read out from the circuit during period t_2 in response to the read signal r_1. This data d_1, represented by the signal XIO, is applied directly to the input bus to buffer **812-12**. Buffer **812-12** is enabled by the high level EQX signal from comparator **801-1** together with the low level signal WXB inverted by inverter **812-13** to produce a high level output signal from NAND gate **805-12**. Thus, the data d_1 on the input bus XIO is transferred to the input bus D of output register **811-1**.

Time Period t_3

On the low-to-high transition of the clock signal at the start of time period t_3, the data d_1 on the input bus D of output register **811-1** is transferred into register **811-1**. The data d_1 is also transferred into data register **809-1** and the address a_3 is transferred into address register **804-1**. Write control signal w_3 is transferred into control register **807-1** and the read control signal r_2 previously in control register **807-1** is transferred through OR gate **805-4** enabled by the low level CSB signal from chip select register **808-1** to control register **807-2**. Thus, the signal WXB goes high. Because during time period t_2 the signal WB is high level, the address signal a_2 in register **804-1** is not transferred into address register **804-2** and the address signal a_1 in address **804-2** remains in address register **804-2**. The write signal w_3 is stored in control register **807-1**. Thus, the signal WB goes low. The address stored in register **804-3** is transferred through the L input bus of mux **803-2** to the address port of memory array **810**. The data previously in data register **809-2** is transmitted through the H input bus of mux **803-7** (selected by the high WXB signal passed through the L input bus of mux **803-6** and the L input bus of mux **803-8**) to the

26

Data In port of memory array **810**. WXB going high disables data registers **809-1** and **809-2** so that on the low-to-high transition of the clock signal at the start of the next time period t_4, the data in these two registers will remain in place and not be transferred. However, the address registers **804-2** and **804-3** are enabled so that the addresses in registers **804-1** and **804-2** can be transferred to registers **804-2** and **804-3**, respectively, on the low-to-high transition of the clock signal at the start of time t_4.

Time period t_4

On the low-to-high transition of the clock signal at the start of time period t_4, address a_4 is loaded into address register **804-1**. Address a_3 previously in address register **804-1** is transferred to address register **804-2** and address a_1 previously in address register **804-2** is transferred to address register **804-3**. The read signal r_4 is transferred into control register **807-1** and the write signal w_3 previously in control register **807-1** is transferred through OR gate **805-4** into control register **807-2**. Thus, the signal WXB goes low. The read signal r_4 means that information d_4 contained in memory array **810** at the location given by address a_4 is to be read out of memory array **810**. If, however, the address a_4 equals the address a_3 stored in address register **804-2** or equals the address a_1 stored in address register **804-3**, the output signal EQX from comparator **801-1**, or the output signal EQY from comparator **801-2**, goes high. If both EQX and EQY are not high, then the data stored at address a_4 is passed through the Data Out port from SRAM **810** and through buffer **812-3** to the input bus of output register **811-1**. On the low-to-high transition of the clock signal at the start of the next time period t_5, this data will be loaded into output register **811-1** and passed through the L input bus of mux **803-5** to buffer **812-4** and then read out of the system. If, however, EQX is high then the address a_4 of the data to be read out from the memory array equals the address a_3 stored in address register **804-2**. The address a_3 corresponds to data d_3 placed on the input bus XIO. EQX being high and WXB being low (to reflect the write signal w_3 stored in control register **807-2**) causes AND gate **805-12** to produce a high output signal to enable buffer **812-12**. The data signal d_3 is thereby passed directly to the input bus of output register **811-1**. This data signal d_3 will then be stored in output register **811-1** on the low-to-high transition of the clock signal at the start of time period t_5.

Alternatively, if EQY is high, then the address a_4 equals the address a_1 stored in address register **804-3**. The address a_1 corresponds to the data d_1 stored in data register **809-1**. Accordingly, the data d_1 (corresponding to the signal DX) is read out of the system through buffer **812-6**. Buffer **812-6** is enabled by a high output signal from AND gate **805-9** caused by a high signal EQY applied to one input lead and low signals EQX and WXB applied to and inverted by inverters **812-8** and **812-9**, respectively. Thus, the data d_1 is transferred through buffer **812-6** to the input bus of output register **811-1** to be loaded into output register **811-1** on the low-to-high transition of the clock signal at the start of the next time period t_5.

The system continues to operate as described above with the data corresponding to a given write signal being written into memory array **810** two write cycles following the loading of the address corresponding to that data into address register **804-1**.

SINGLE PIPELINE OPERATION OF THE CIRCUIT OF FIG. 9

While the circuit in FIG. **9** has been described in conjunction with the dual pipeline operation, the single pipeline

27

operation of the circuit requires the signal S/DB to be high. Thus, muxes **803-1**, **803-3**, **803-5**, **803-6** and **803-8** will all have their high input buses selected for the transmission of signals to the output bus from the mux. FIG. **10C** illustrates the timing waveforms associated with the system shown in FIG. **9** for the single pipeline delay.

Time Period t_0

On the low-to-high transition of the clock signal at the start of time period t_0 (a time arbitrarily selected after the system has begun operating), address a_0 is read into address register **804-1**. Read signal r_0 is read into control register **807-1**. Thus, the signal WB is high and thus the address a_0 is transmitted directly through the H input bus of mux **803-2** to the address port of memory array **810**.

The address a_{-1} is transferred simultaneously into address register **804-2** and address register **804-3**, the latter register receiving the output signal from mux **803-1**, the input signal to mux **803-1** being applied to the H input bus directly from the output bus of register **804-1**. If address a_0 equals address a_{-1} stored in both registers **804-2** and **804-3**, then both EQX and EQY from comparators **801-1** and **801-2** are high. The high EQY signal causes mux **803-4** to pass the DX signal reflecting the data signal in register **809-1** through the H input bus of mux **803-4** to the H input bus of mux **803-5** and from there through buffer **812-4** to the XIO pin of the circuit. Because EQY is high, the signal DX is the data d_{-1} stored in data register **809-1**. Note that in the single pipeline mode, signals EQX and EQY are both simultaneously high or simultaneously low because the same address is stored in both data registers **804-2** and **804-3**.

Time Period t_1

On the low-to-high transition of the clock signal at the start of time period t_1, the address signal a_1 is written to address register **804-1**. Because the signal WB is high at the start of time period t_1, the address registers **804-2** and **804-3** retain their contents, namely the address a_{-1} in both registers. Because a write signal w_1 is stored in control register **807-1** and the previous read signal r_0 is stored in control register **807-2**, the signal WB is low and the signal RB is high. Because the write operation is to take place, and because WB is low, the address a_{-1} stored in address register **804-3** is transmitted directly through the L input bus of mux **803-2** (selected because the control signal WB is low). The data d_{-1} in data register **809-1** is then written into memory array **810** at the address a_{-1} stored in address registers **804-2** and **804-3**.

Time Period t_2

On the low-to-high transition of the clock signal at the start of time period t_2, the address signal a_2 is written to address register **804-1**. Because the signal WB is low at the start of time period t_2, the address a_1 in address register **804-1** is transferred to register **804-2** and also to **804-3**. On the low-to-high transition of the clock signal at the start of time period t_2, the write signal w_2 is transferred into control register **807-1**. The previous write signal w_1 stored in control register **807-1** is transferred to control register **807-2**. Thus the signal WXB is low as is the signal WB. The data d_1 is stored in data register **809-1** and the data d_{-1} is transferred from data register **809-1** to data register **809-2**. Because WB is low, the address a_1 in address register **804-3** is transmitted directly to the address port of SRAM **810** and the data d_1 in data register **809-1** is transmitted directly to the Data In port of SRAM **810** to be stored there at address a_1. The data d_2 corresponding to the address a_2 is placed on the Data I/O pin during the time period t_2.

28

Time Period t_3

On the low-to-high transition of the clock signal at the start of time period t_3, the address signal a_3 is read into address register **804-1**. Simultaneously the data d_2 placed on the input bus XIO during the latter portion of time period t_2 is read into data register **809-1** and the data d_1 previously in data register **809-1** is transferred to data register **809-2**. Both of these registers are enabled at the start of time period t_3 by the low level write signal w_2 stored in control register **807-1** during time period t_2. This low level signal is transferred through the H input bus of mux **803-6** and through one input lead of OR gate **805-5** to enable these two data registers.

On the low-to-high transition of the clock signal at the start of time period t_3, the signal w_2 in control register **807-1** is transferred to control register **807-2** and the signal r_3, a read signal, is transferred into control register **807-1**. The signal WB becomes high level thereby selecting the H input bus of mux **803-2** which passes the address a_3 from address register **804-1** through mux **803-2** to the address port associated with memory array **810**. Simultaneously the address a_2 previously in address register **804-1** is stored in address registers **804-2** and **804-3**.

If address a_3 equals address a_2, then both EQX and EQY go high thereby both disabling buffer **812-3**. EQY high selects the H input bus of mux **803-4** which thereby passes to the H input bus of mux **803-5** and through the output buffer **812-4** to the XIO port the data d_2 associated with the address a_2.

Thus, the single pipeline delay system operates to either read out of memory the data at the address associated with a read control signal or to read out of a data storage register the data associated with the address of the location in memory to be read from when that address is the immediately preceding address of data to be written to the memory.

While several embodiments of this invention have been described, other embodiments of this invention will be obvious to those skilled in the art. In particular, embodiments involving three or more pipeline delays will be obvious in view of this disclosure. Also, while a single Data I/O terminal is shown in FIGS. **7**, **7A** and **7B**, for example, for receiving data to be written into or being read from the memory **710**, in practice separate data input and data output terminals can be used, if desired.

I claim:

1. A structure which comprises:

a memory;

an input circuit coupled to receive a memory address, a read/write control signal and write data to be written into the memory, said input circuit including one or more storage registers for storing the write data to be written into the memory prior to writing the write data into the memory, the storage registers being capable of receiving and storing the write data on a rising edge of a clock signal; and

a logic circuit for causing the stored write data to be written from the input circuit into the memory during a pth write operation following the write operation during which said write data was placed in said storage registers, while causing the write data to be held in the storage registers during any intervening read and write operations, where p is a selected integer.

2. A structure as in claim **1** including:

means for holding the write data in said storage registers during one or more read operations immediately following the write operation during which said write data was placed in said storage registers.

3. A structure as in claim **1** including:

means for reading out read data from said memory or from one of said storage registers during one or more read operations following said write operation, said read data being read from one of said storage registers when the memory address to be read from the structure corresponds to the memory address of the write data

previously stored in one of said storage registers, and said read data being read from the memory when the memory address of said read data does not correspond to the memory address of the write data previously stored in one of said storage registers.

* * * * *